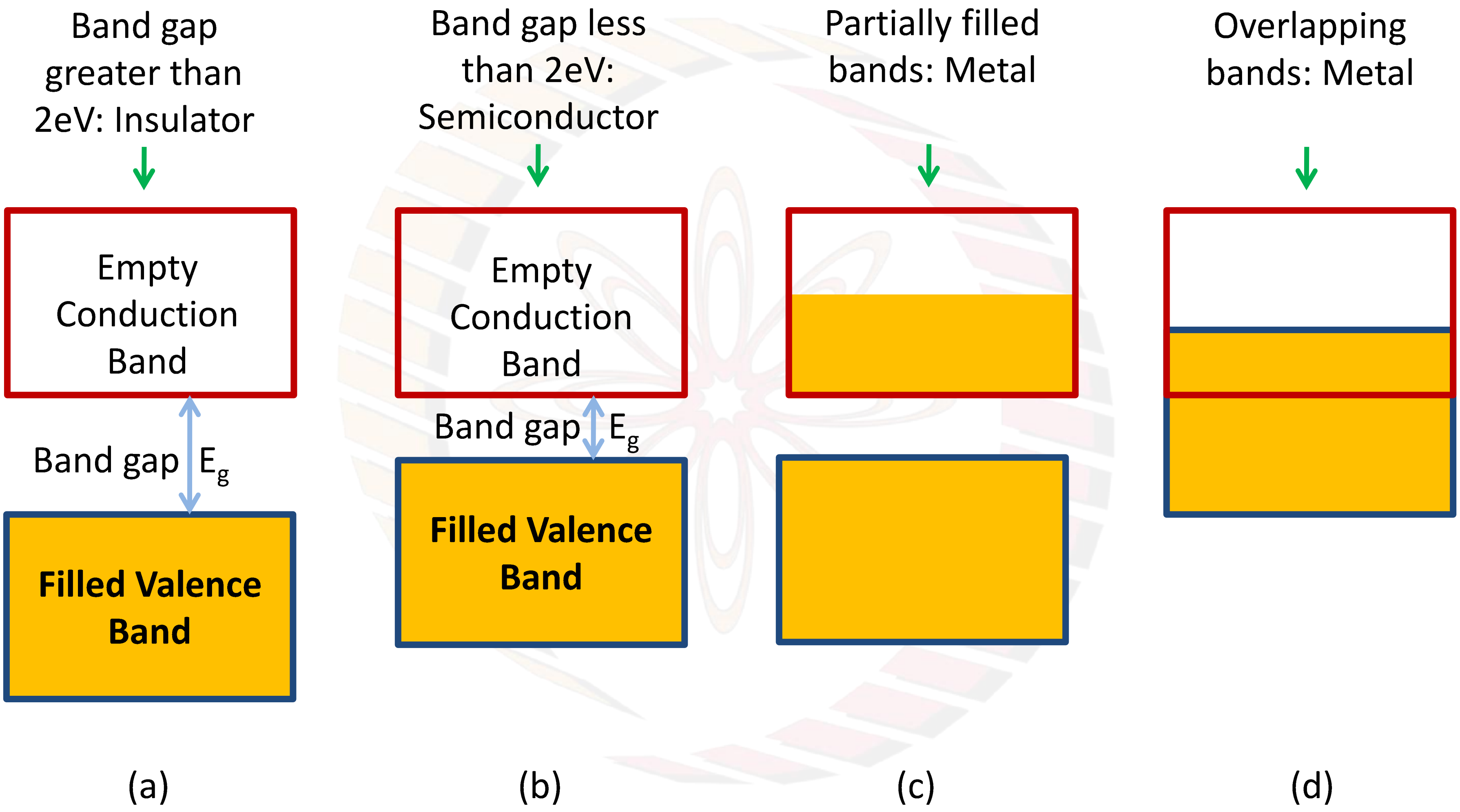
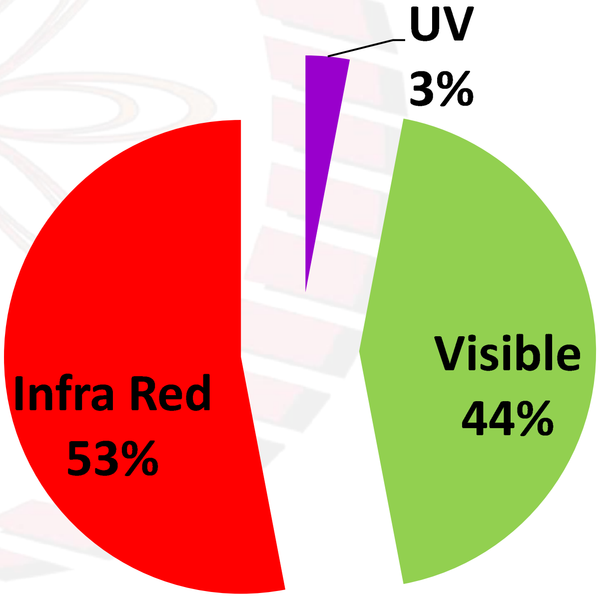
Solar Energy:
The Semiconductor

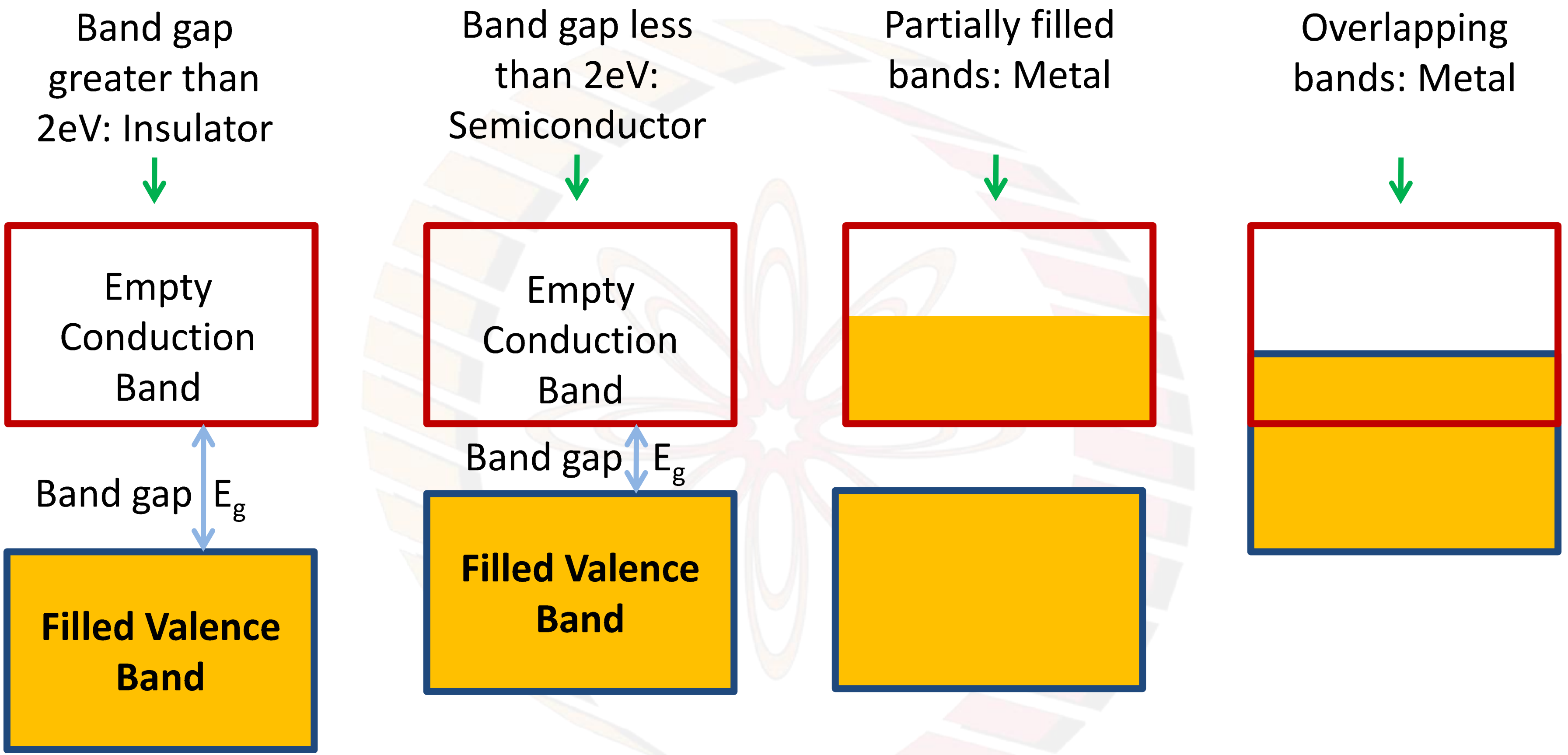
Learning objectives:

1) To plot the band diagrams of materials
2) To explain the interaction of bands with radiation
3) To understand the different ways in which band diagrams can be plotted.

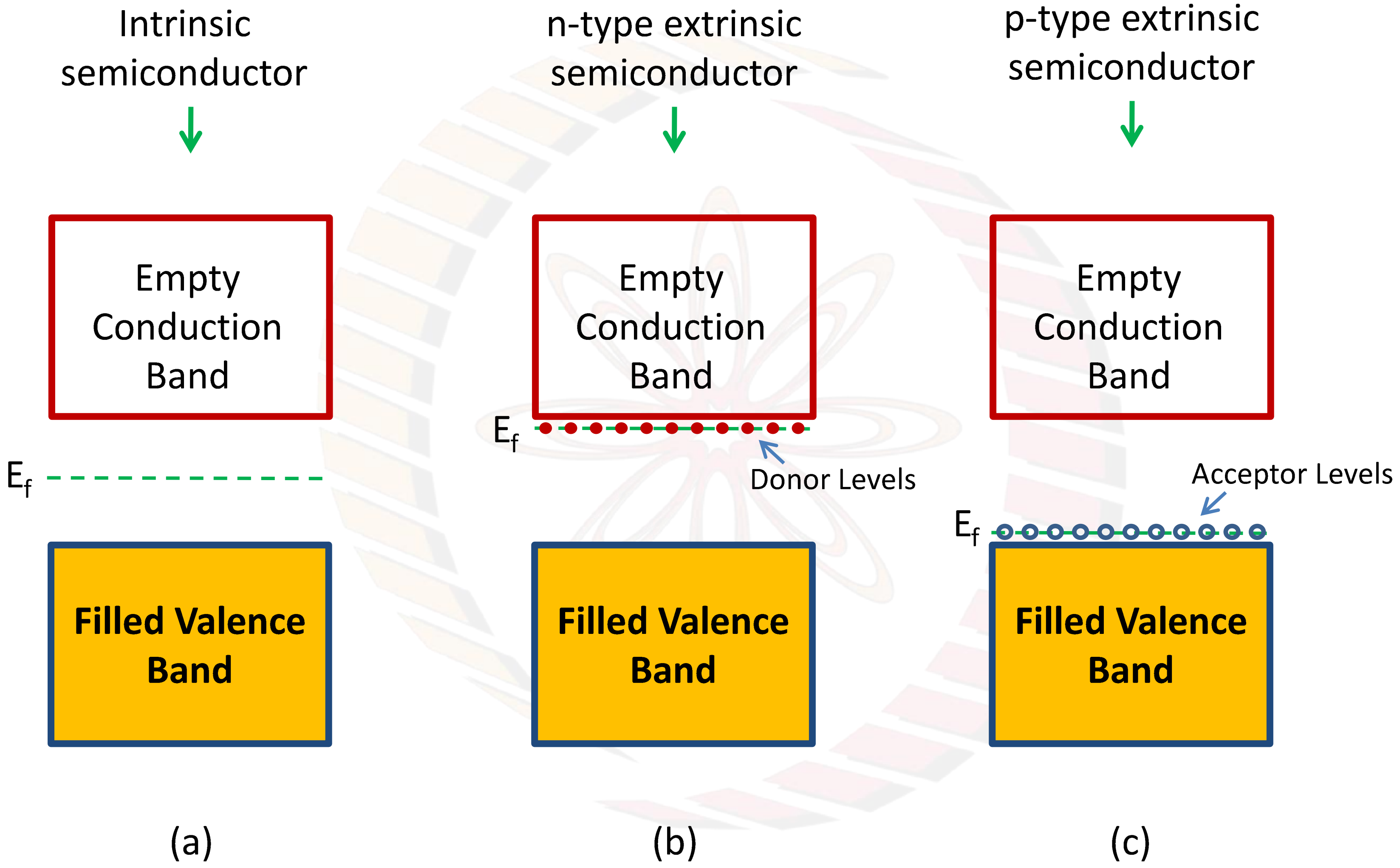

Band gap greater than 2eV: Insulator
Empty Conduction Band
Band gap E_g
Filled Valence Band
(a)
Band gap less than 2eV: Semiconductor
Empty Conduction Band
Band gap E_g
Filled Valence Band
(b)
Partially filled bands: Metal
(c)
Overlapping bands: Metal
(d)

Visible Spectrum Wavelength:	400 nm (violet)	to	700 nm (red)
Corresponding band gaps:	3.1 eV	to	1.8 eV

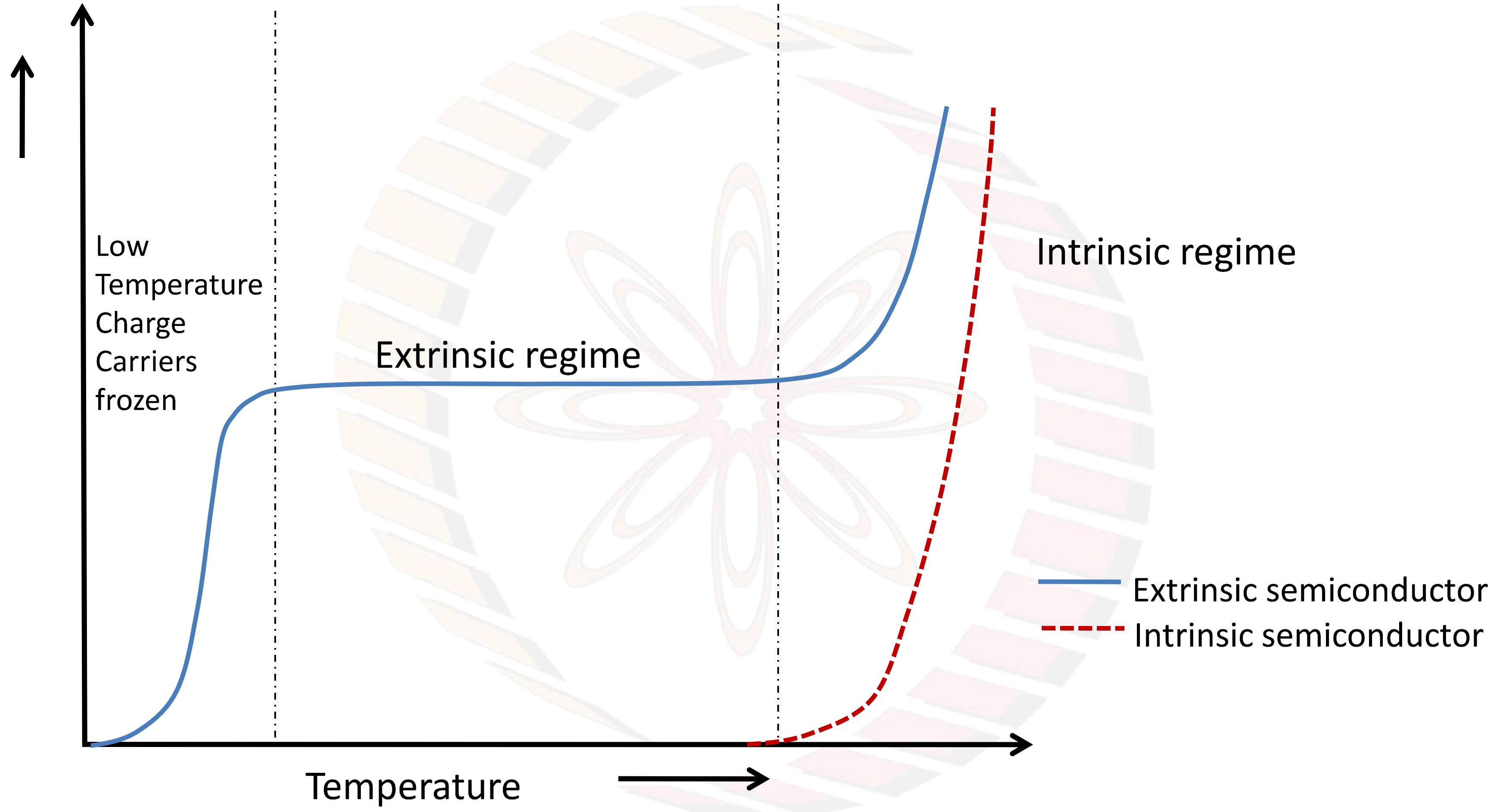




Visible Spectrum Wavelength:	**400 nm (violet)**	**to**	**700 nm (red)**
Corresponding band gaps:	**3.1 eV**	**to**	**1.8 eV**



Intrinsic semiconductor
n-type extrinsic semiconductor
p-type extrinsic semiconductor
Empty Conduction Band
Empty Conduction Band
Empty Conduction Band
E_f
E_f
Donor Levels
Acceptor Levels
E_f
Filled Valence Band
Filled Valence Band
Filled Valence Band
(a)
(b)
(c)


Low
Temperature
Charge
Carriers
frozen
Extrinsic regime
Intrinsic regime
Extrinsic semiconductor
Intrinsic semiconductor
Temperature

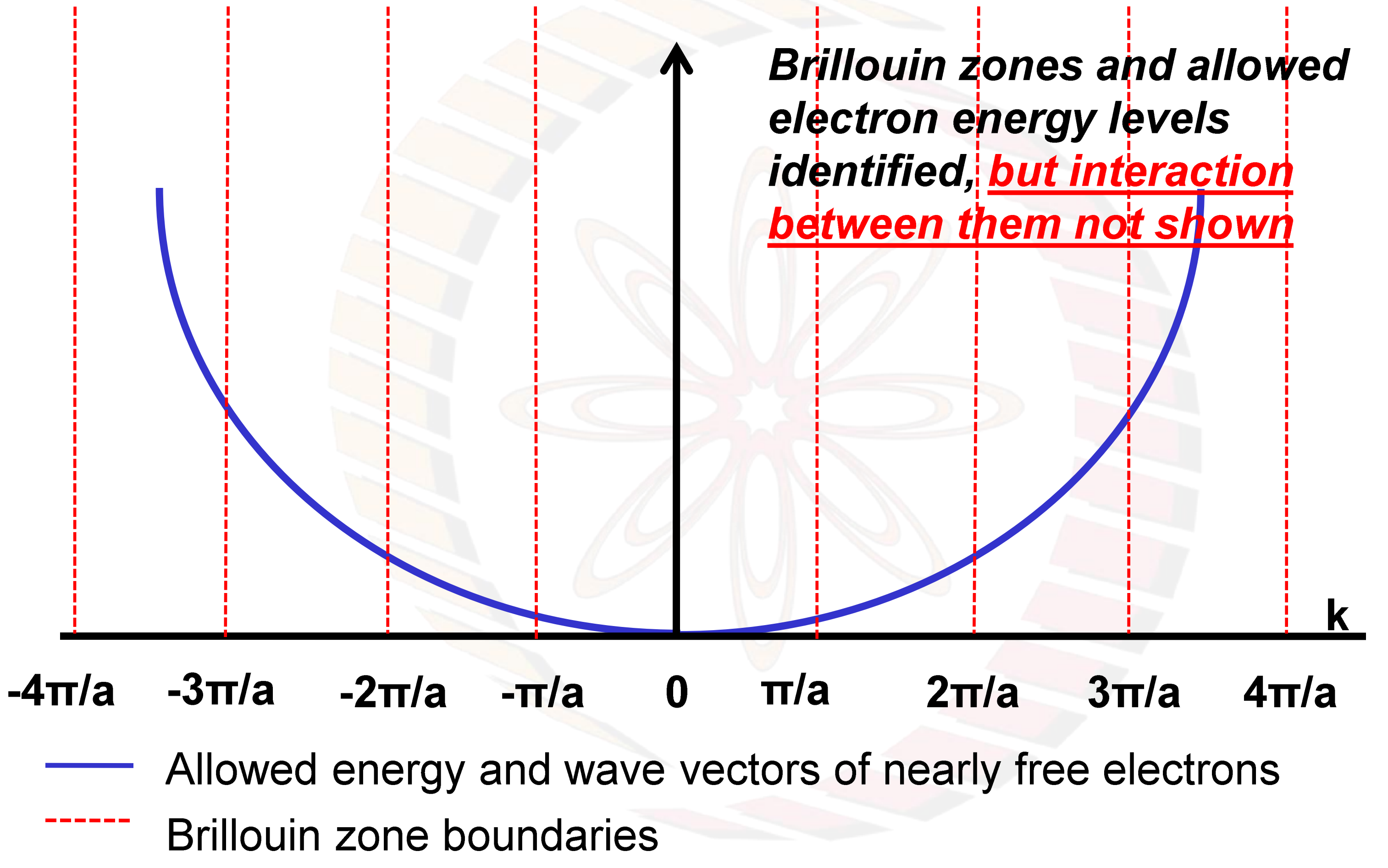
$E = h\nu$

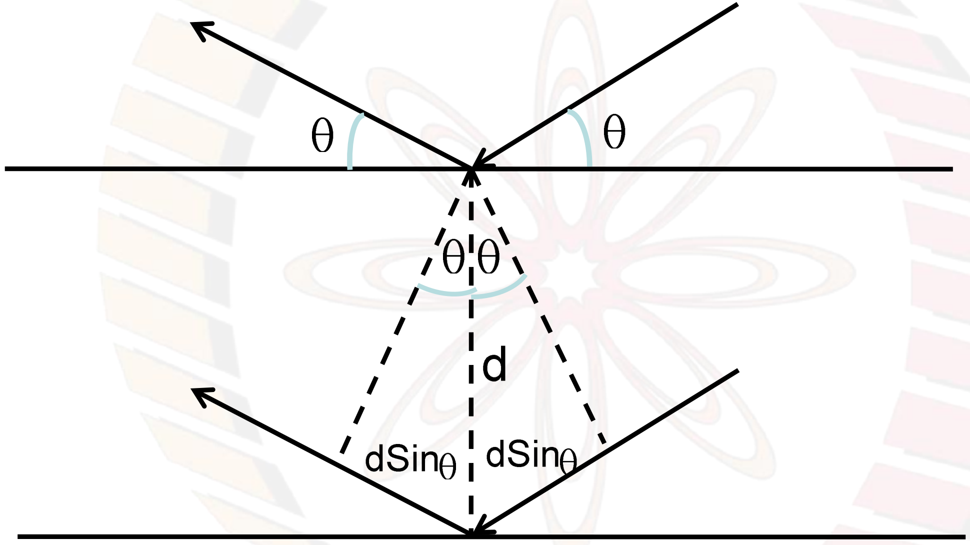
$\lambda = \dfrac{h}{p}$

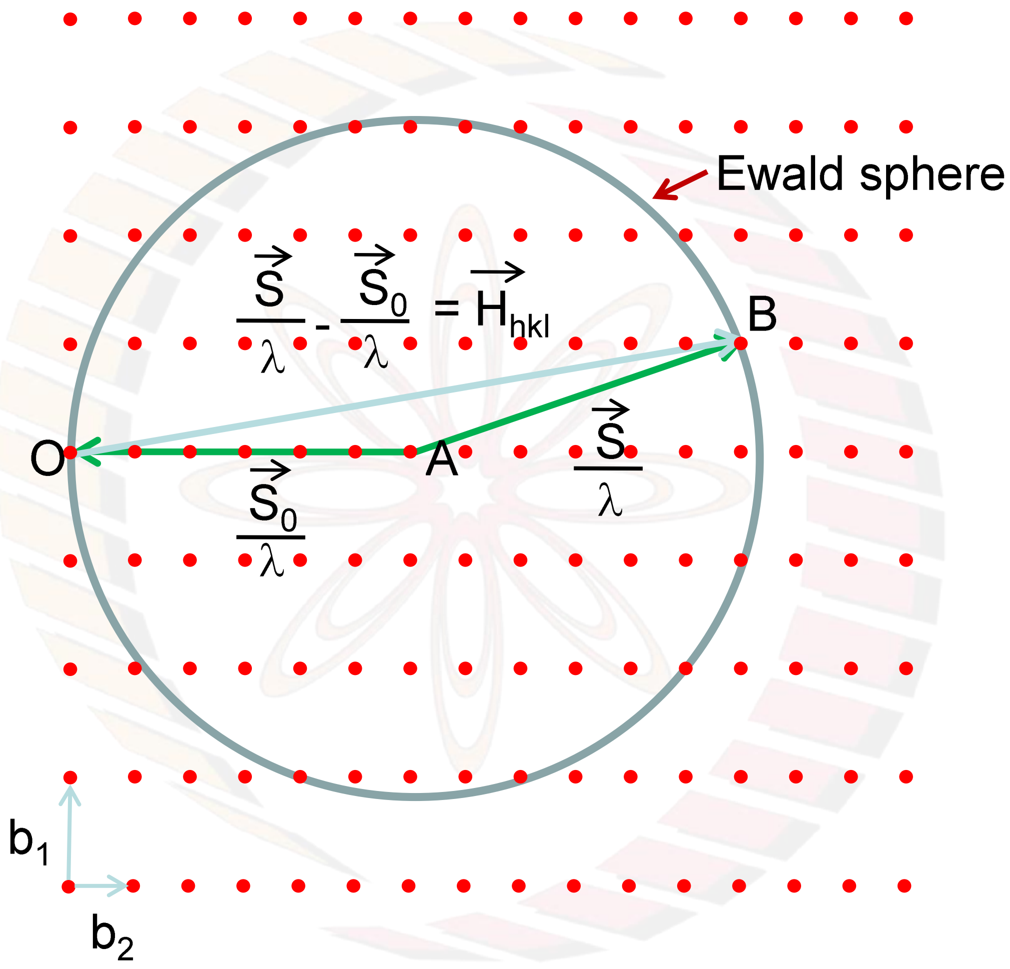
Planck

de Broglie

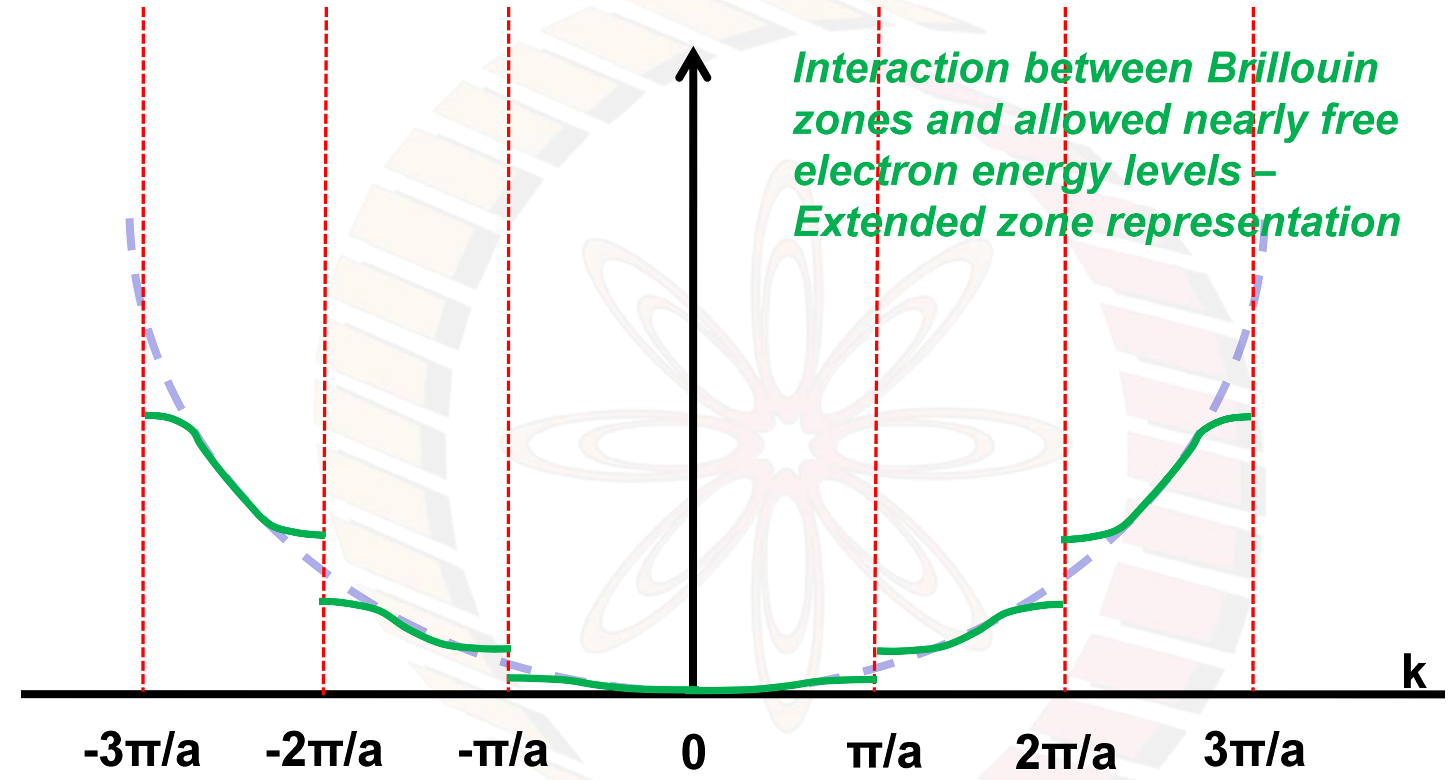
$$E = \frac{\hbar^2 k^2}{2m}$$


Brillouin zones and allowed electron energy levels identified, but interaction between them not shown
k
-4π/a
-3π/a
-2π/a
-π/a
0
π/a
2π/a
3π/a
4π/a
Allowed energy and wave vectors of nearly free electrons
Brillouin zone boundaries


θ
θ
θ θ
d
dSinθ
dSinθ



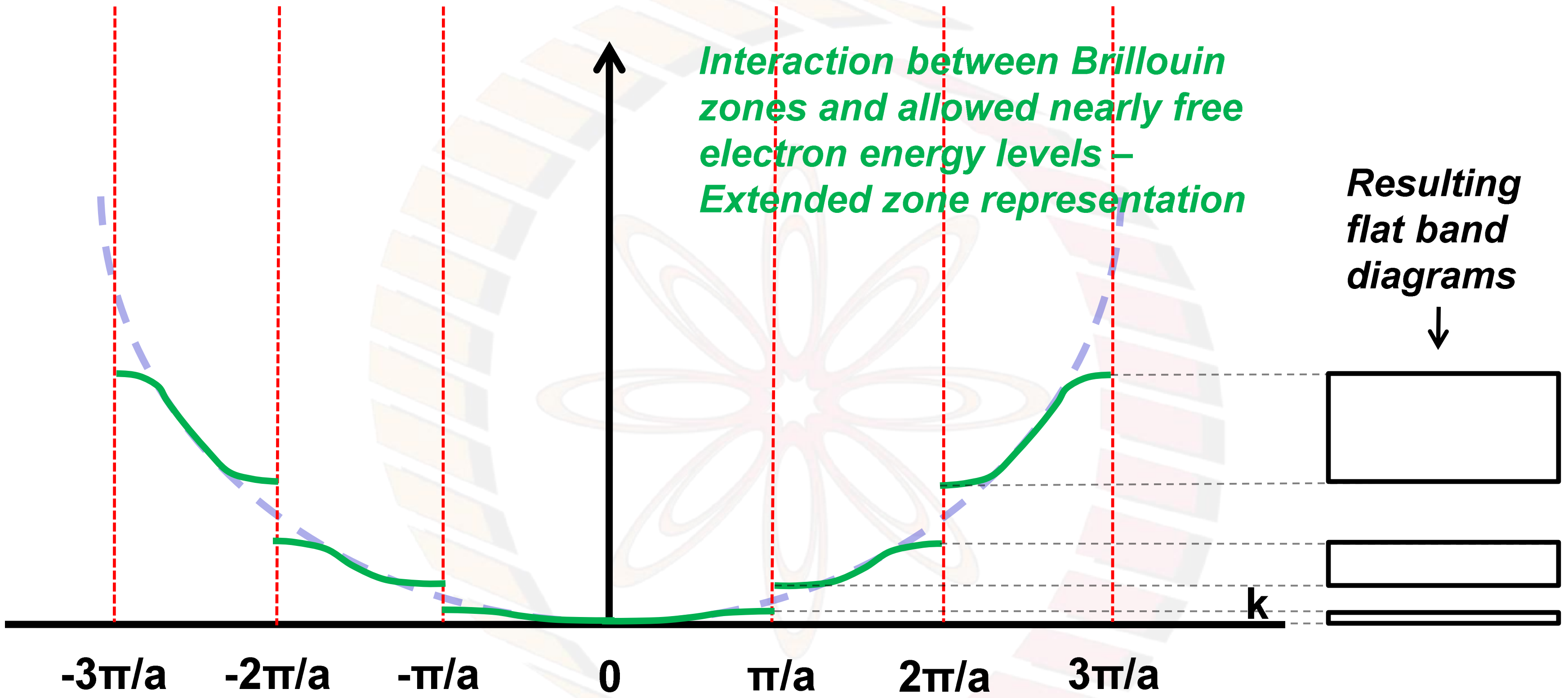
Ewald sphere
$\frac{\vec{S}}{\lambda} - \frac{\vec{S}_0}{\lambda} = \vec{H}_{hkl}$
B
O
A
$\frac{\vec{S}_0}{\lambda}$
$\frac{\vec{S}}{\lambda}$
b_1
b_2



E Vs k of nearly free electrons, without accounting for the Brillouin Zones

E Vs k of nearly free electrons, distorted due to interaction with Brillouin Zones

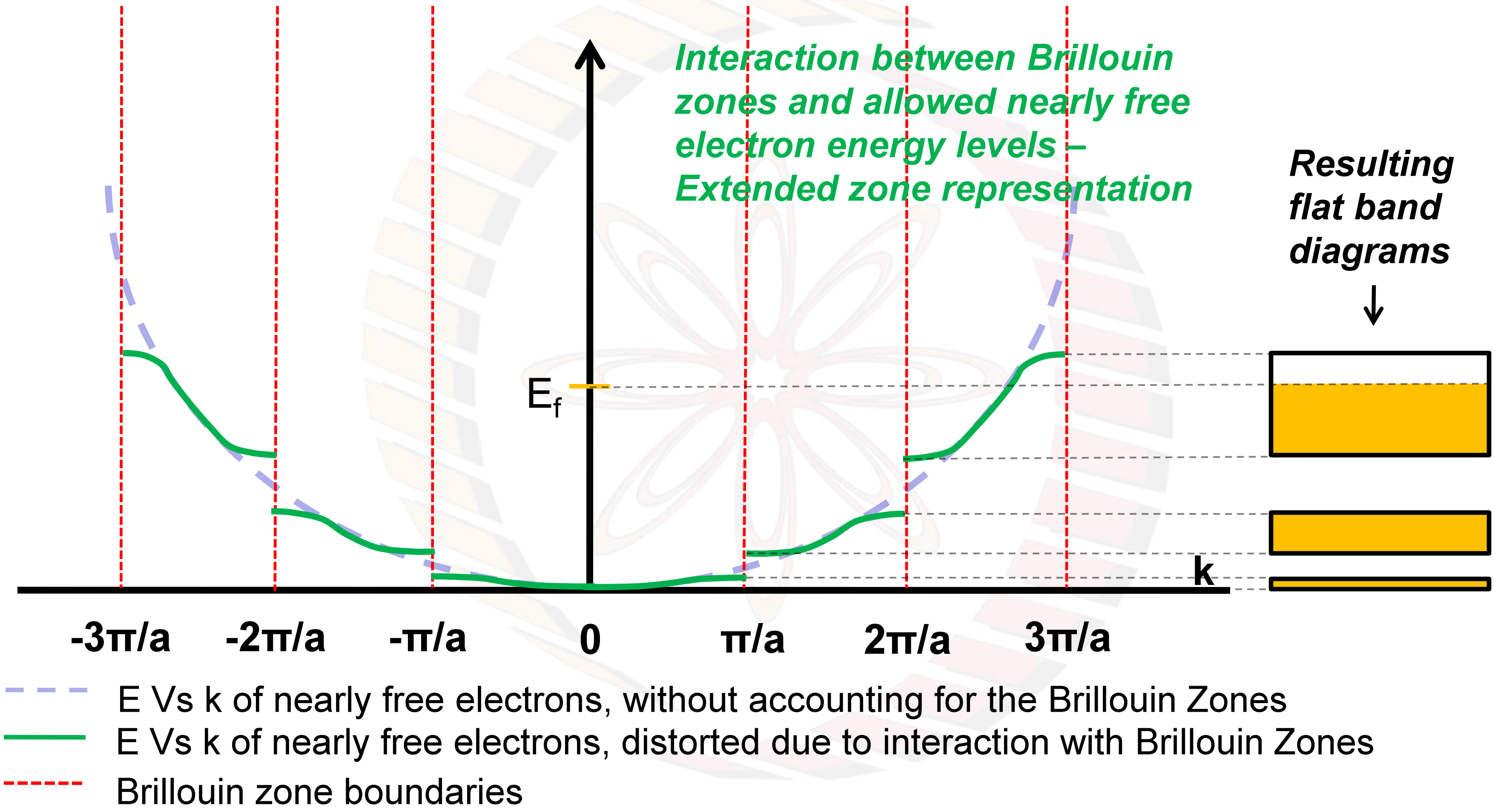
Brillouin zone boundaries



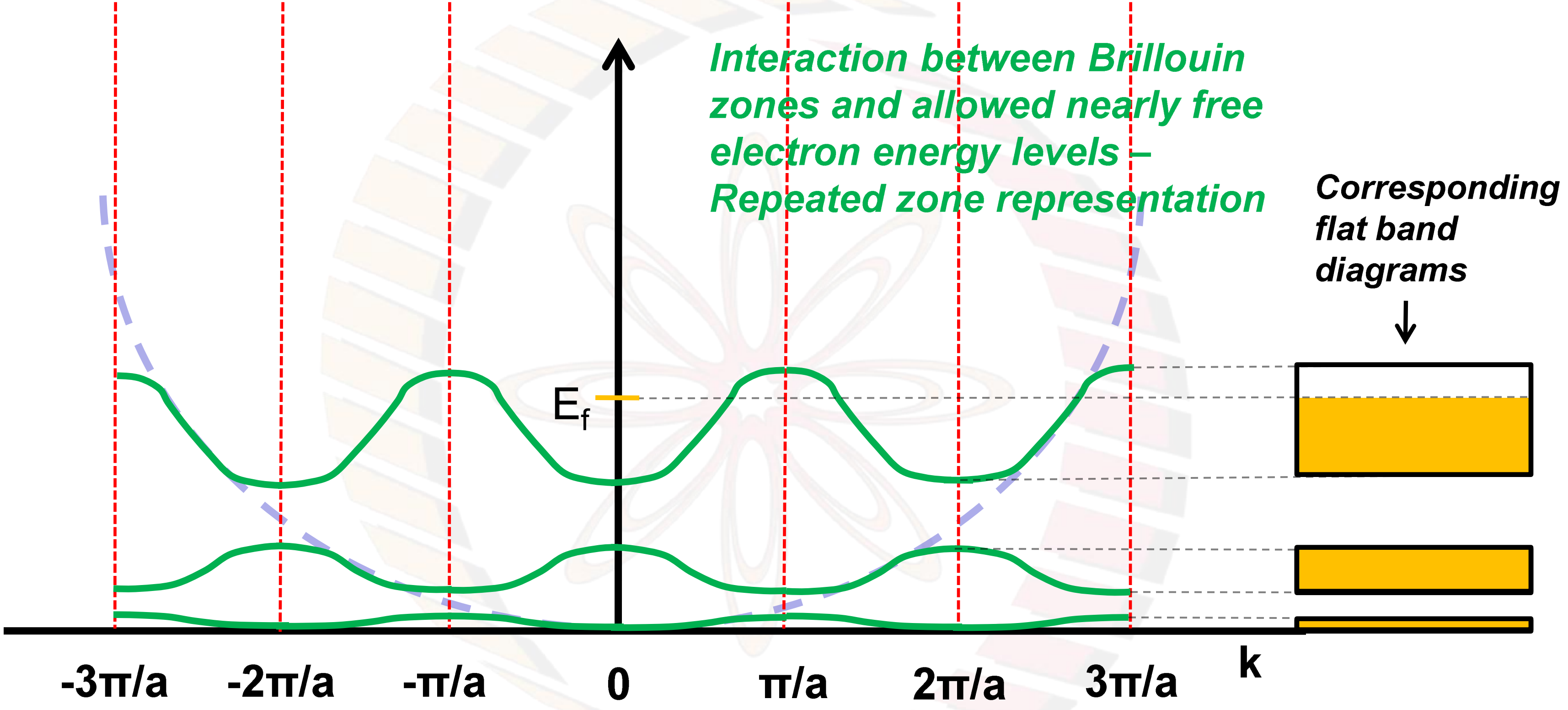
E Vs k of nearly free electrons, without accounting for the Brillouin Zones

E Vs k of nearly free electrons, distorted due to interaction with Brillouin Zones

Brillouin zone boundaries



Interaction between Brillouin zones and allowed nearly free electron energy levels – Extended zone representation
Resulting flat band diagrams
E_f
k
-3π/a
-2π/a
-π/a
0
π/a
2π/a
3π/a
E Vs k of nearly free electrons, without accounting for the Brillouin Zones
E Vs k of nearly free electrons, distorted due to interaction with Brillouin Zones
Brillouin zone boundaries

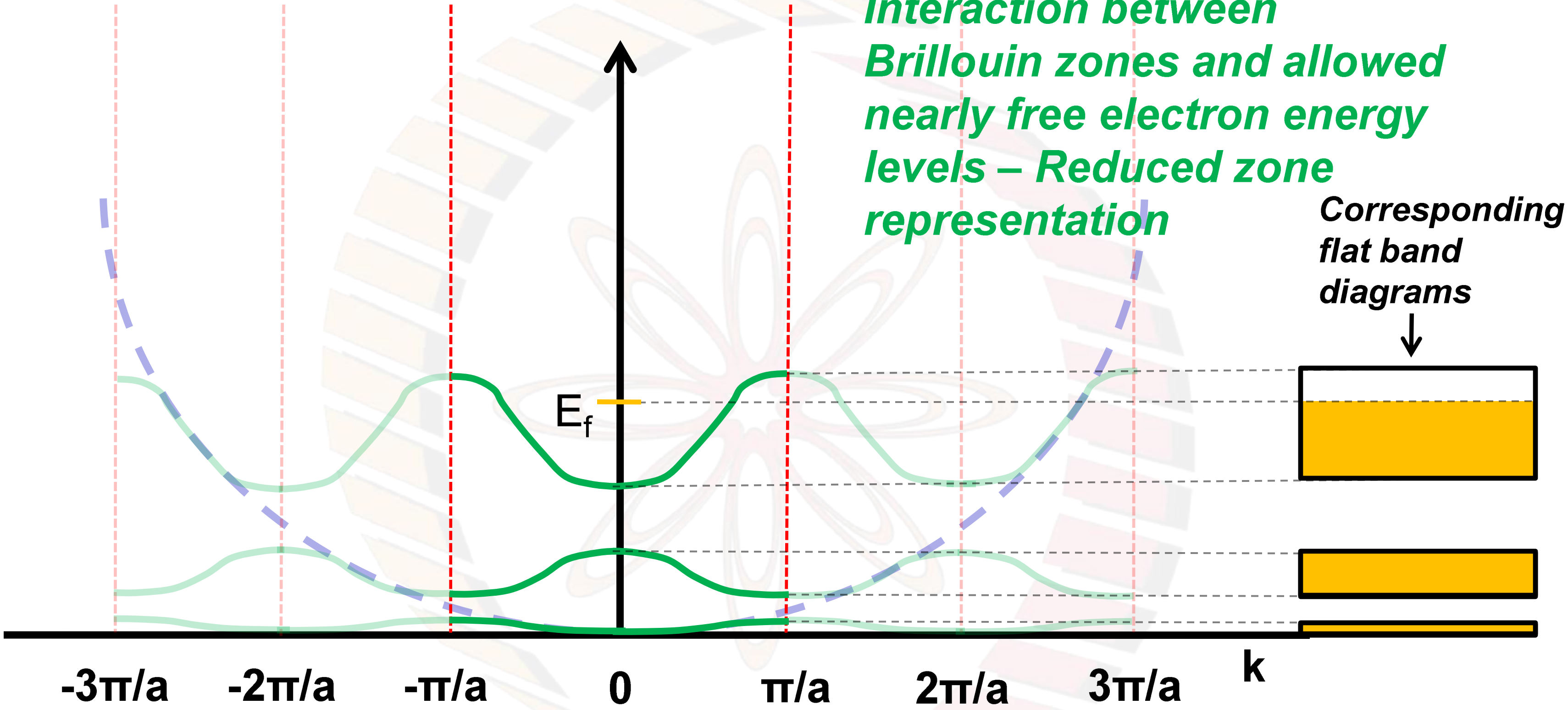


E Vs k of nearly free electrons, without accounting for the Brillouin Zones

E Vs k of nearly free electrons, distorted due to interaction with Brillouin Zones

Brillouin zone boundaries

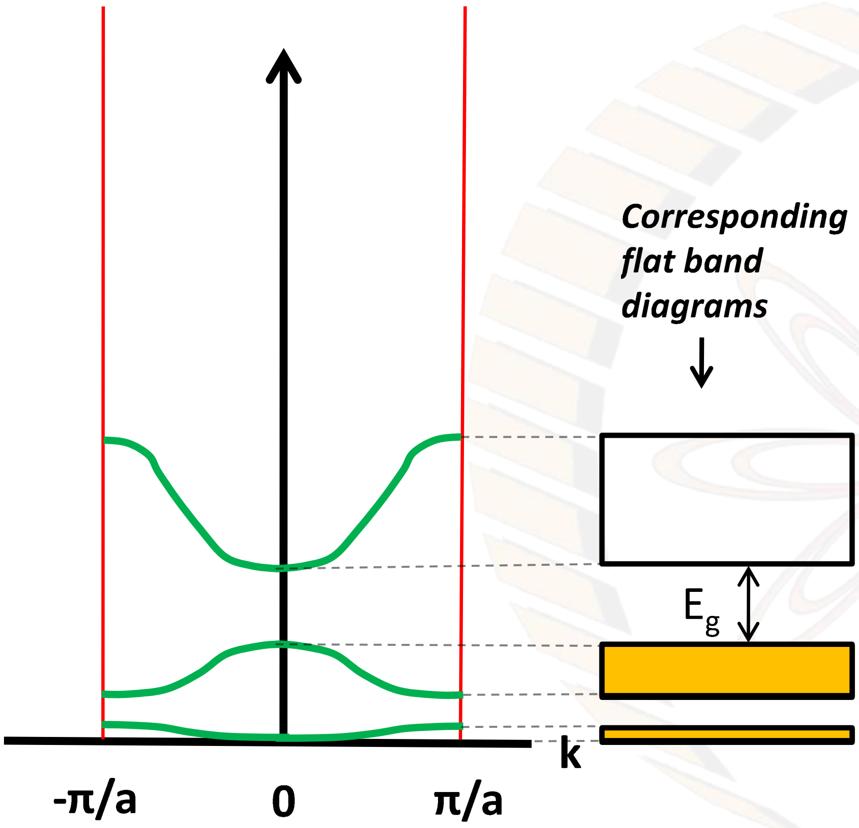
Interaction between Brillouin zones and allowed nearly free electron energy levels – Reduced zone representation



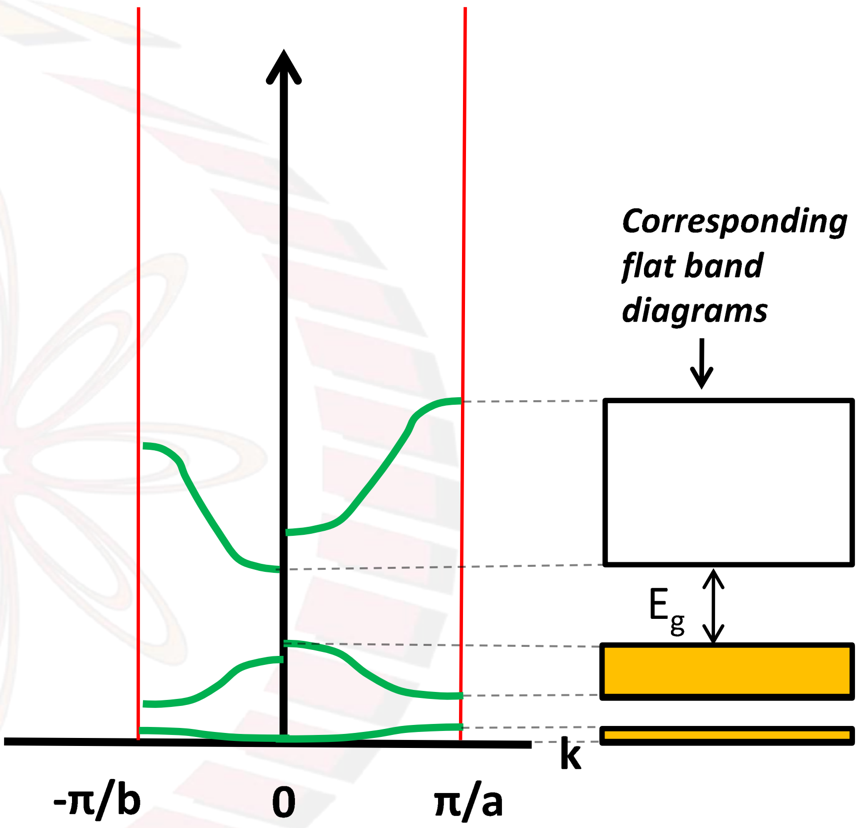
E Vs k of nearly free electrons, without accounting for the Brillouin Zones

E Vs k of nearly free electrons, distorted due to interaction with Brillouin Zones

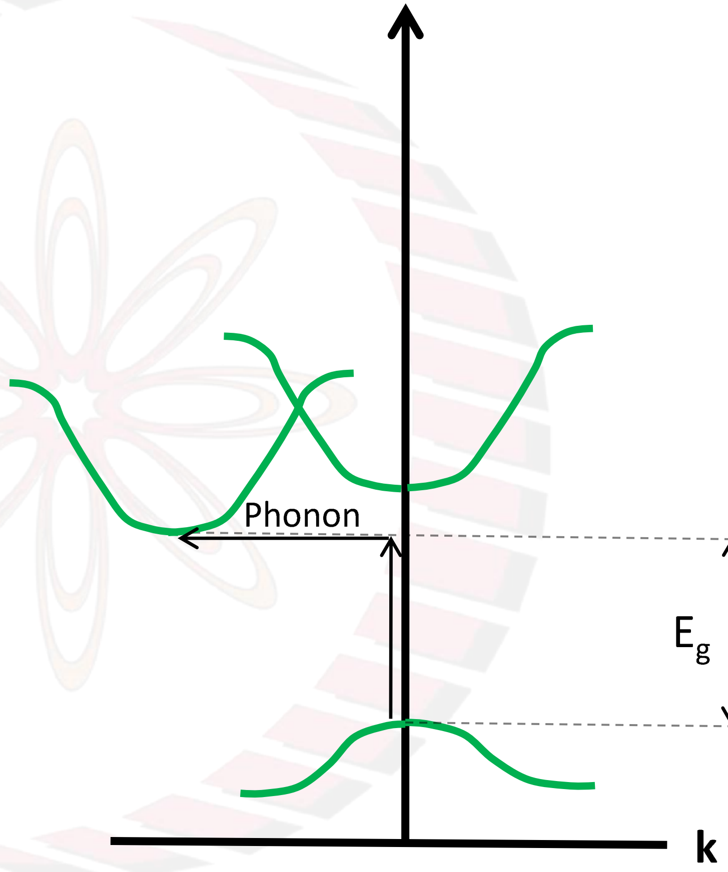
Brillouin zone boundaries



Direct bandgap semiconductor



Indirect bandgap semiconductor


Phonon
E_g
k

Conclusions:

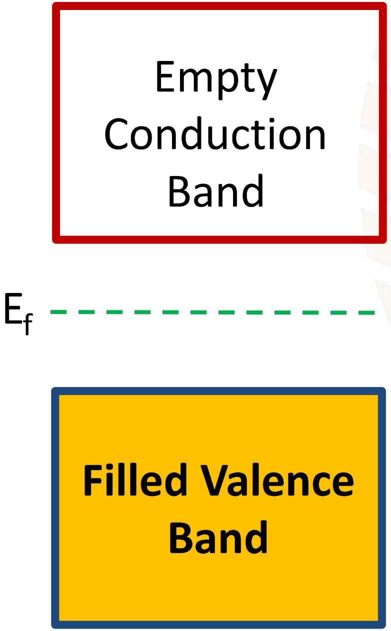
1) There is significant variation in the band diagrams of different types of materials
2) Interaction of a material with radiation depends strongly on its band diagram
3) Visible spectrum is a small fraction of solar radiation
4) There is a difference in the effectiveness with which direct and indirect bandgap semiconductors interact with radiation

Solar Energy:
The p-n junction

Learning objectives:

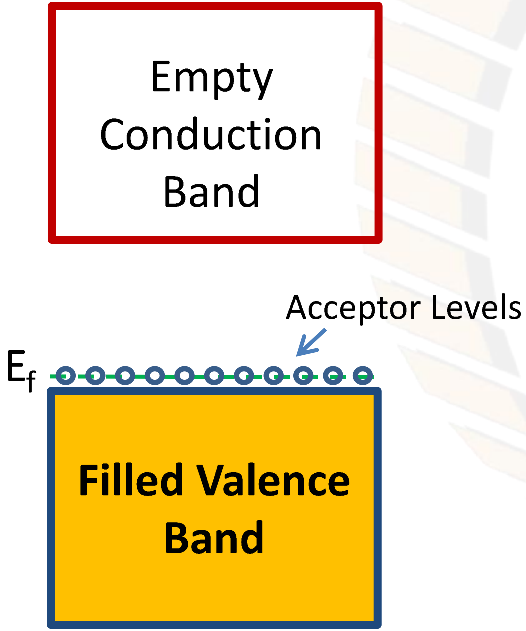
1) To describe the material features as well as characteristics of the p-n junction
2) To explain the functioning of the p-n junction

Intrinsic semiconductor



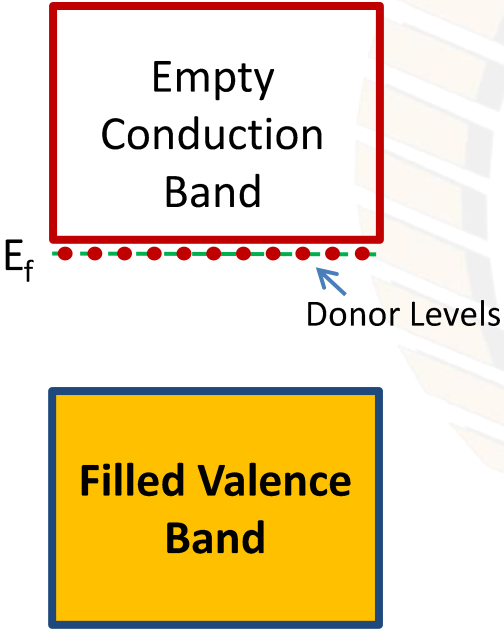
- Charge carrier concentration depends only temperature
- Conductivity depends only on Temperature
- Examples:
  - Elemental: Group IV A: Si (1.1 eV), Ge (0.7 eV)
  - Compound:
    - Group III A and Group V A (III-V)
      - GaAs, InSb
    - Group II B and Group VI A (II-VI)
      - CdS, ZnTe

p-type extrinsic semiconductor

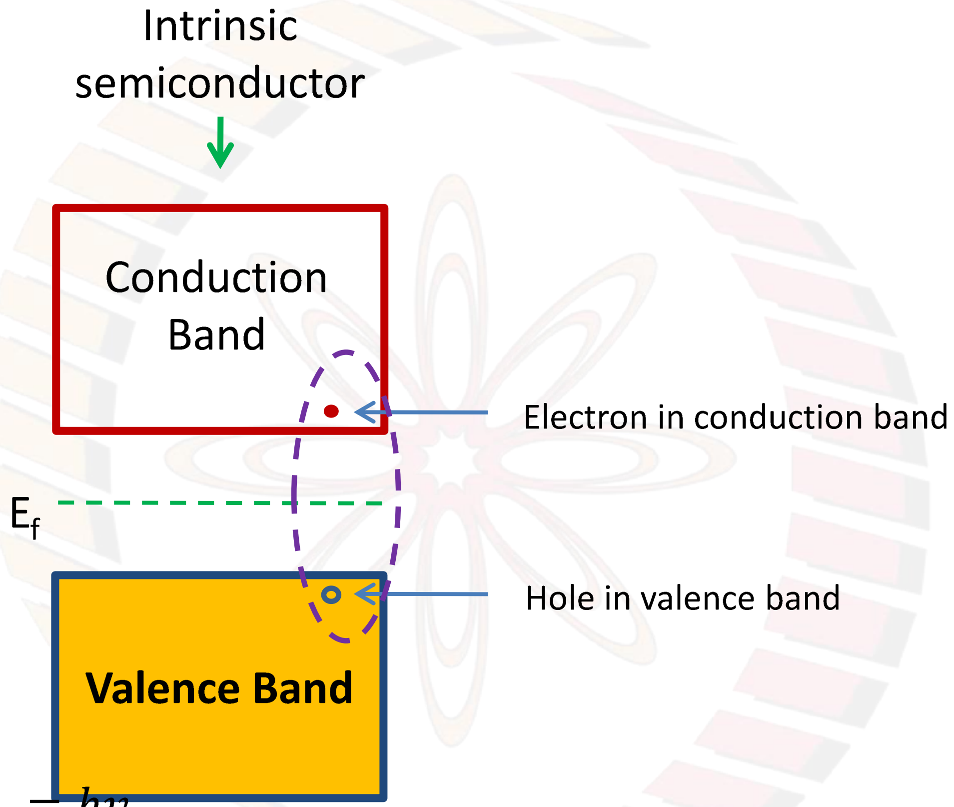


- Charge carrier concentration depends on dopant concentration
- Conductivity depends on dopant concentration
- Examples:
  - Group IV A elements doped with small quantities of Group III A elements: B, Al, Ga, In, Tl

n-type extrinsic semiconductor



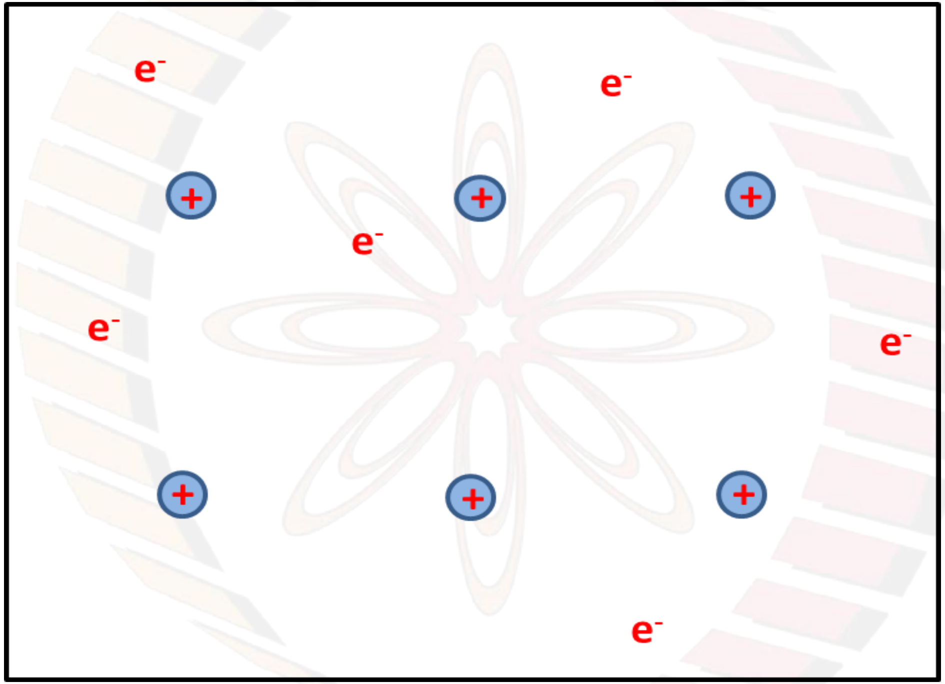
- Charge carrier concentration depends on dopant concentration
- Conductivity depends on dopant concentration
- Examples:
  - Group IV A elements doped with small quantities of Group V A elements: N, P, As, Sb, Bi



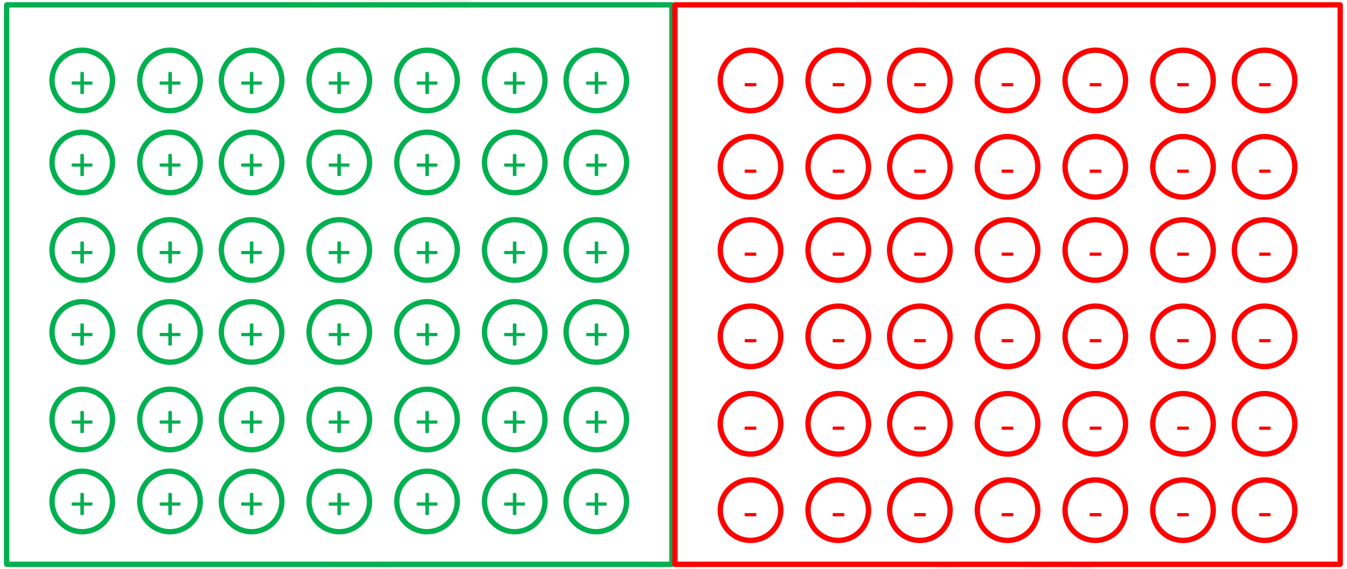
$$E_g = h\nu$$

Stability of electron-hole pair?

Metal



The p-n junction

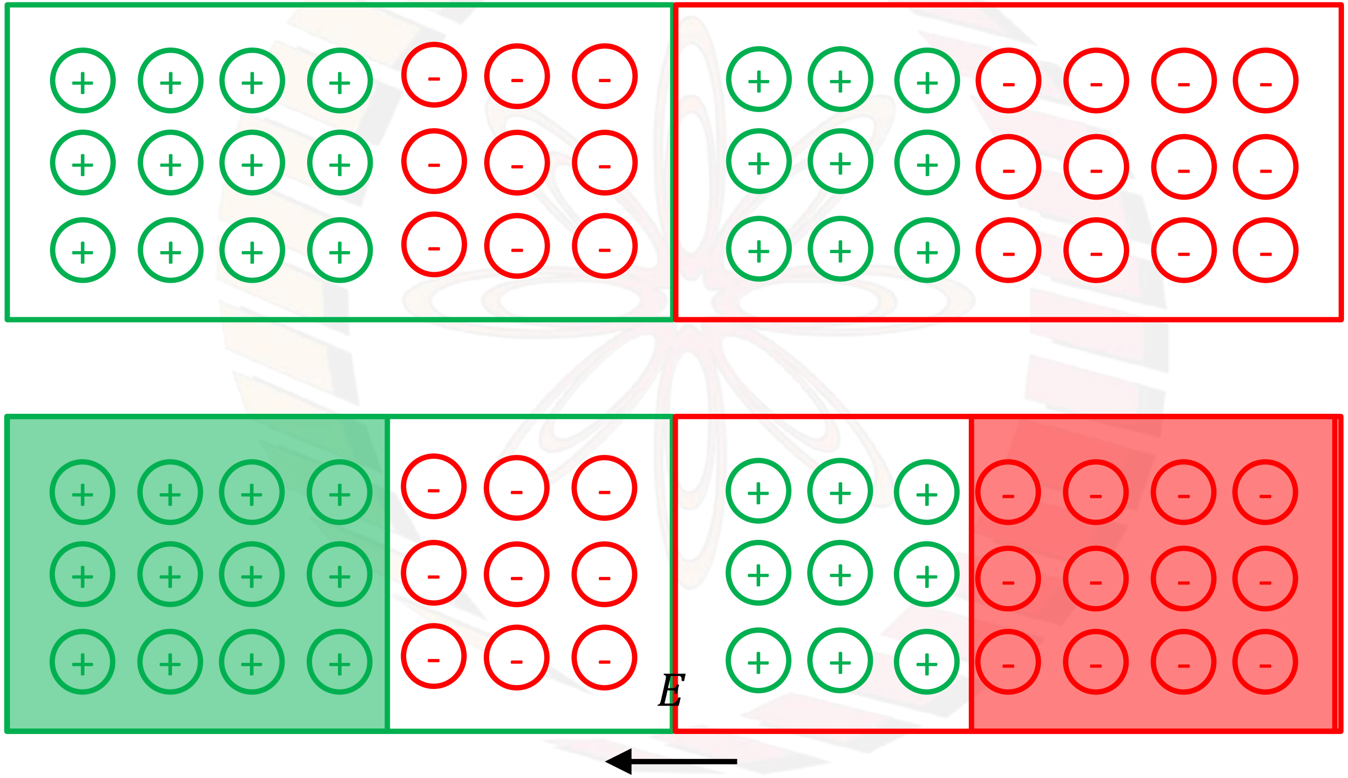


Si doped with B

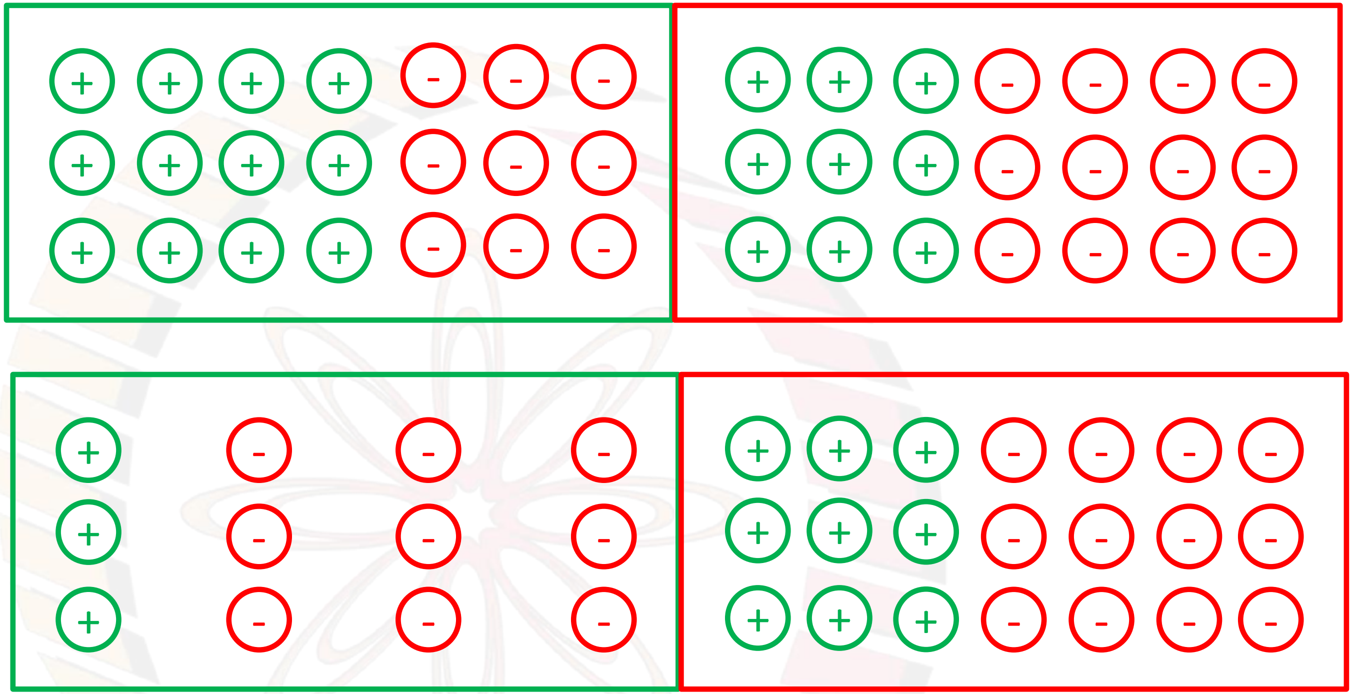
$$\sigma = n\,e\,\mu_e + p\,e\,\mu_h$$

Si doped with P

The space charge region
Depletion region

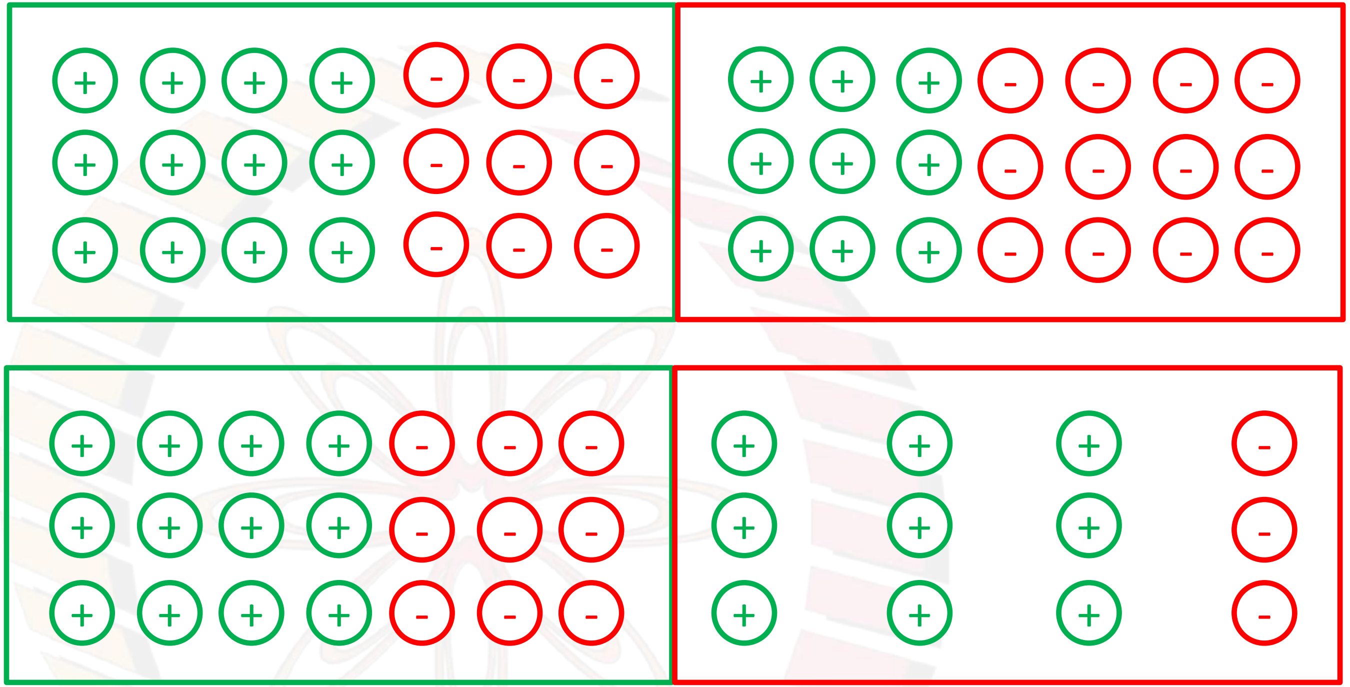


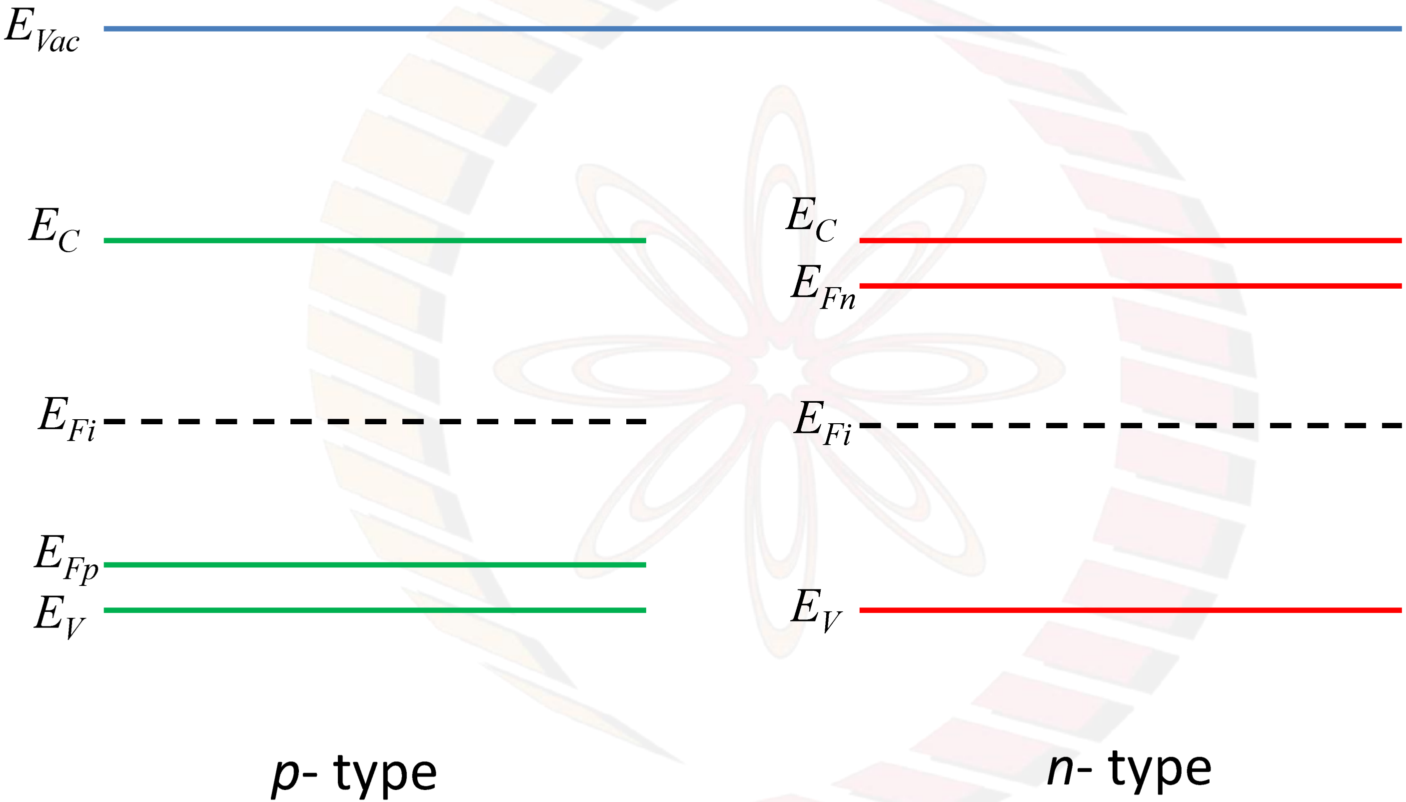
space charge region
depletion region

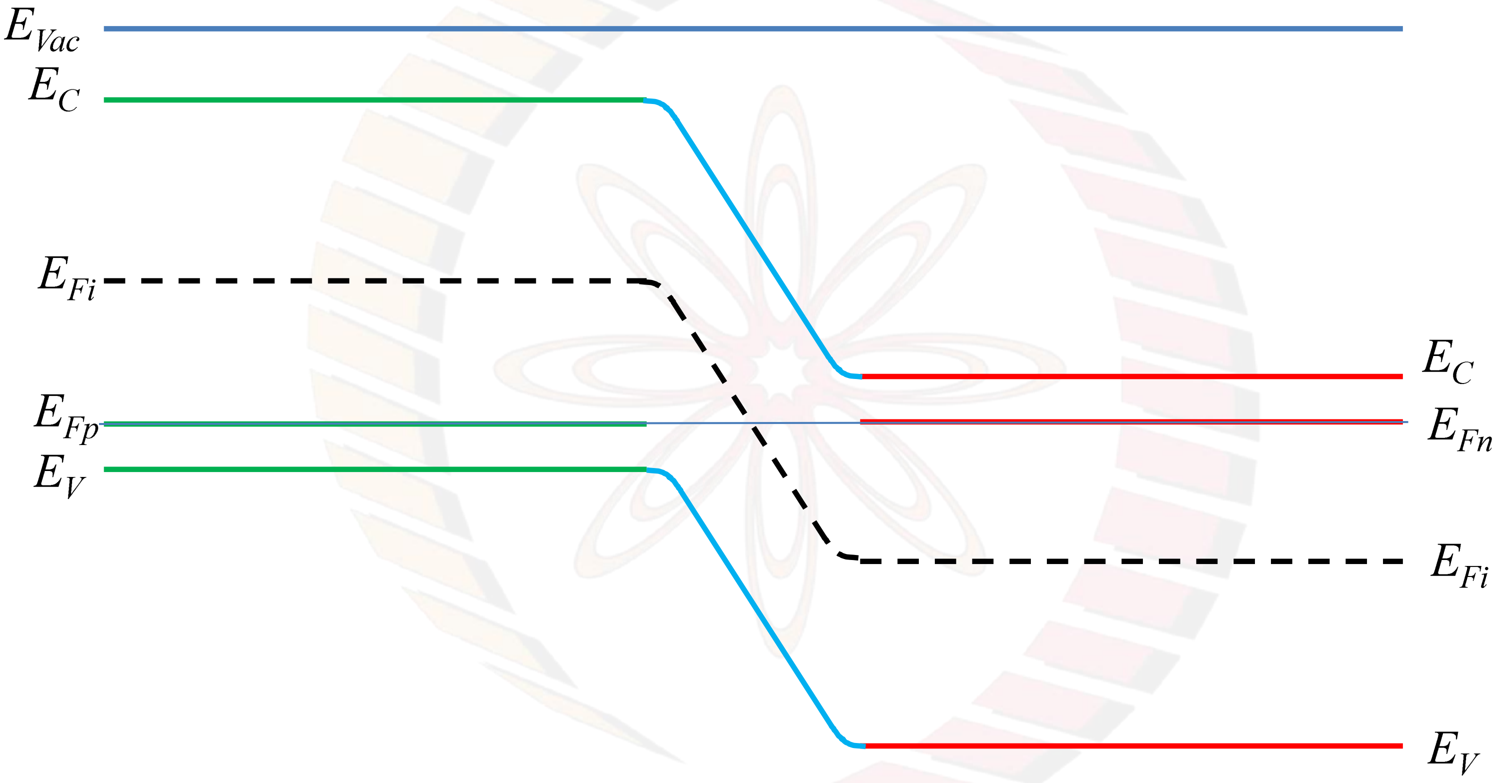


space charge region

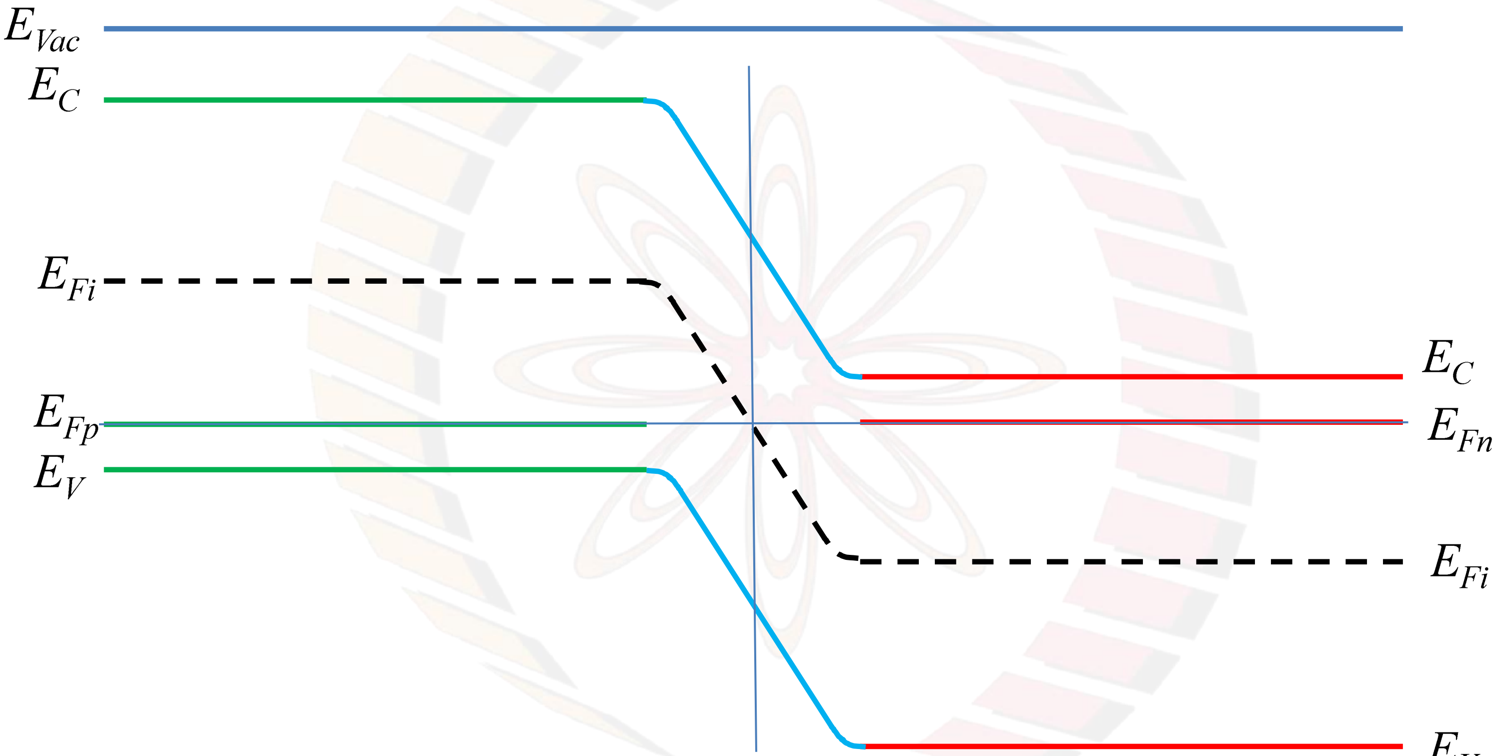
depletion region




E_{Vac}
E_C
E_{Fi}
E_{Fp}
E_V
E_C
E_{Fn}
E_{Fi}
E_V
p- type
n- type

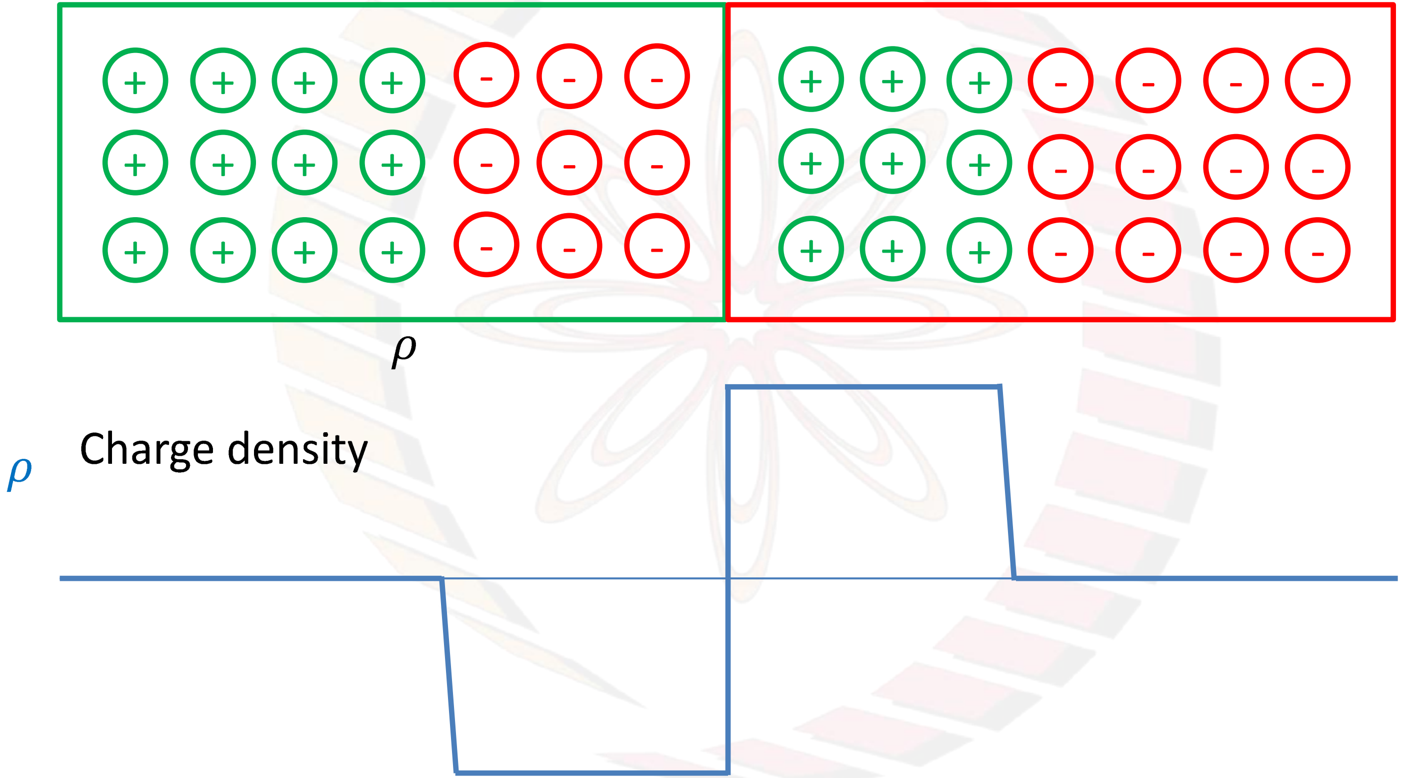


pn-junction

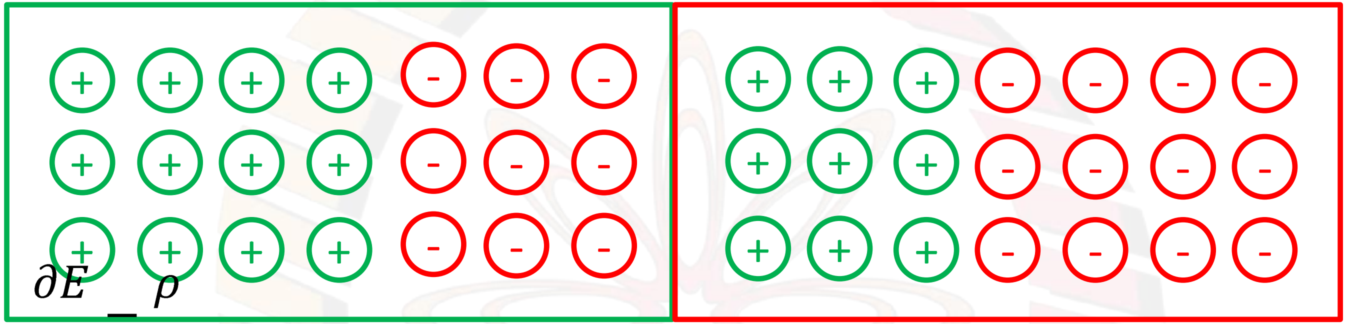


pn-junction

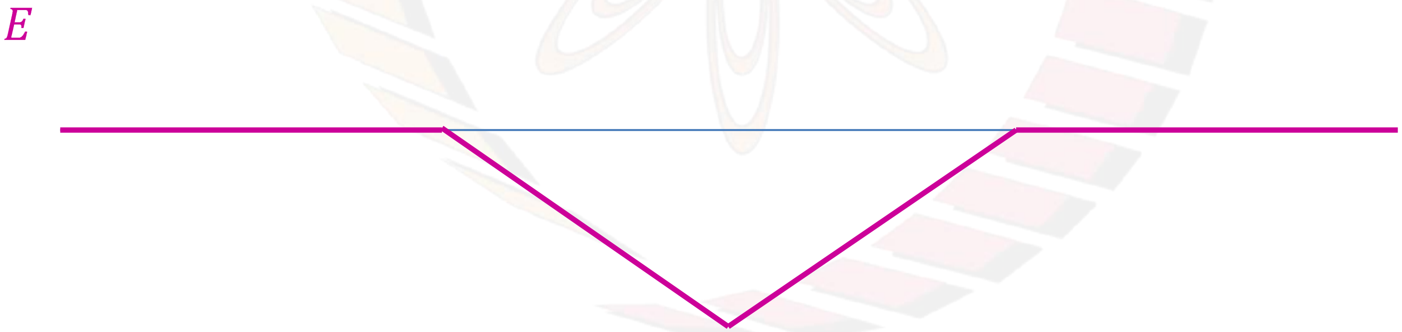
The space charge region



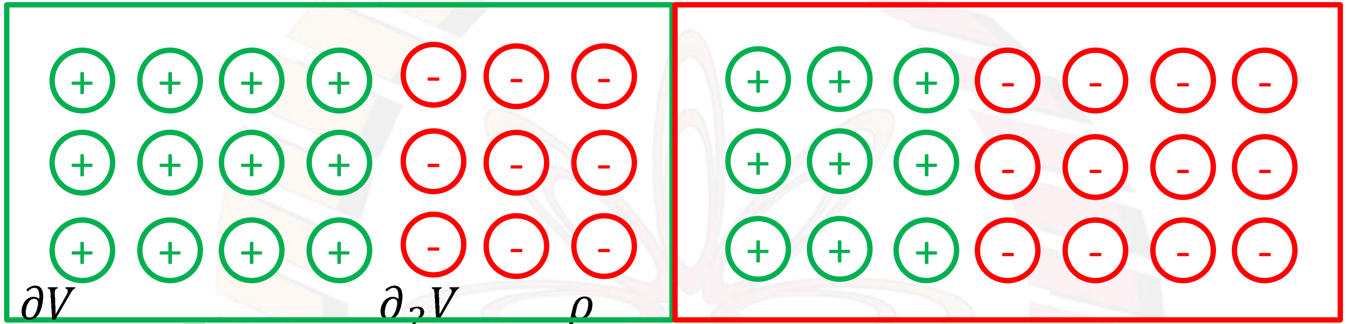
The space charge region



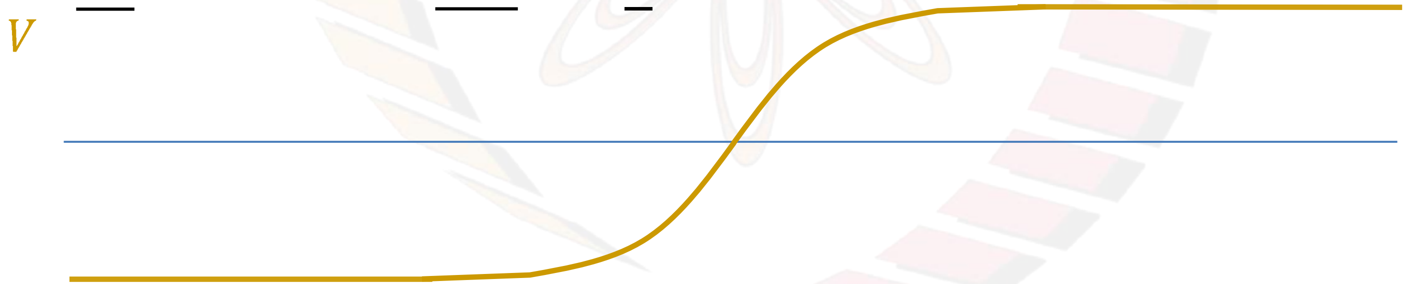
$$\frac{\partial E}{\partial x} = \frac{\rho}{\varepsilon}$$

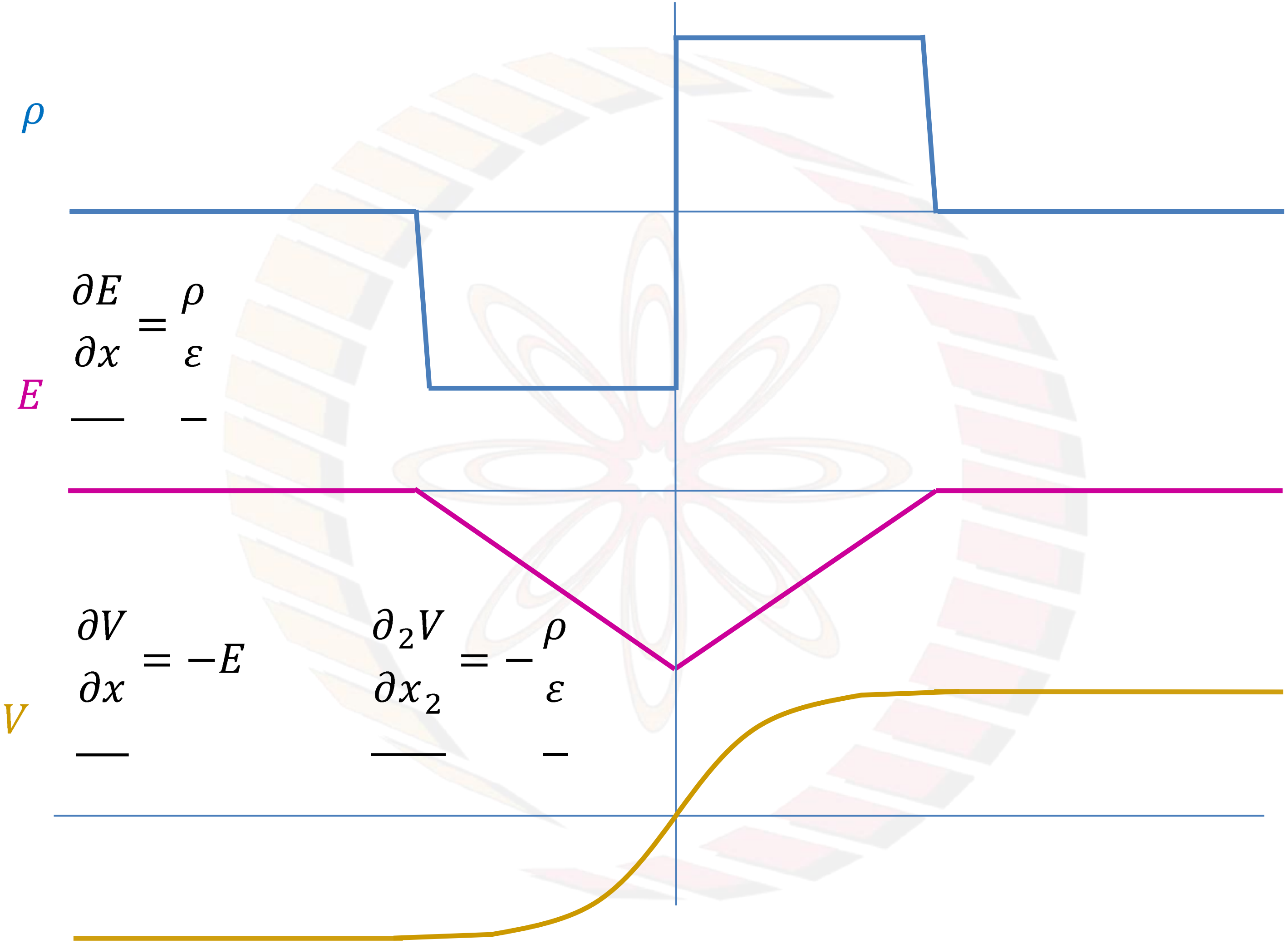


The space charge region



$$\frac{\partial V}{\partial x} = -E \qquad \frac{\partial_2 V}{\partial x_2} = -\frac{\rho}{\varepsilon}$$



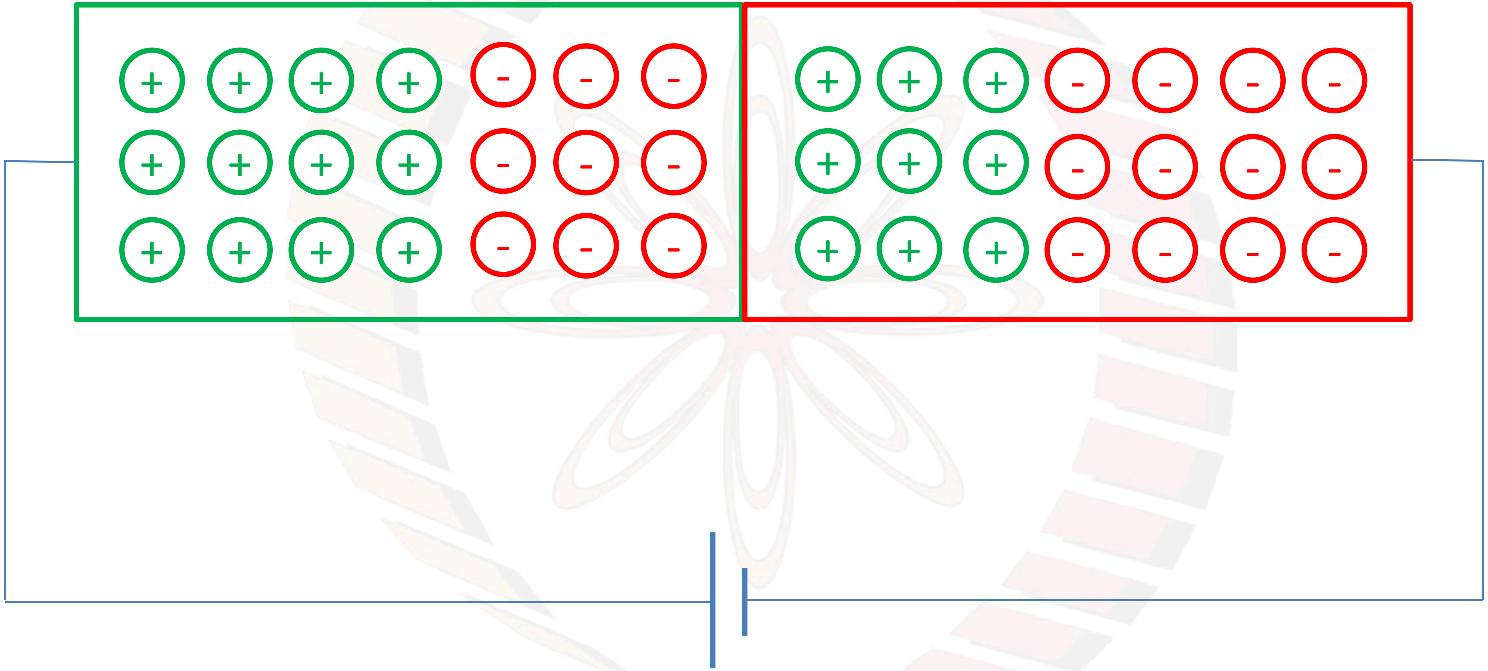


$$\frac{\partial E}{\partial x} = \frac{\rho}{\varepsilon}$$

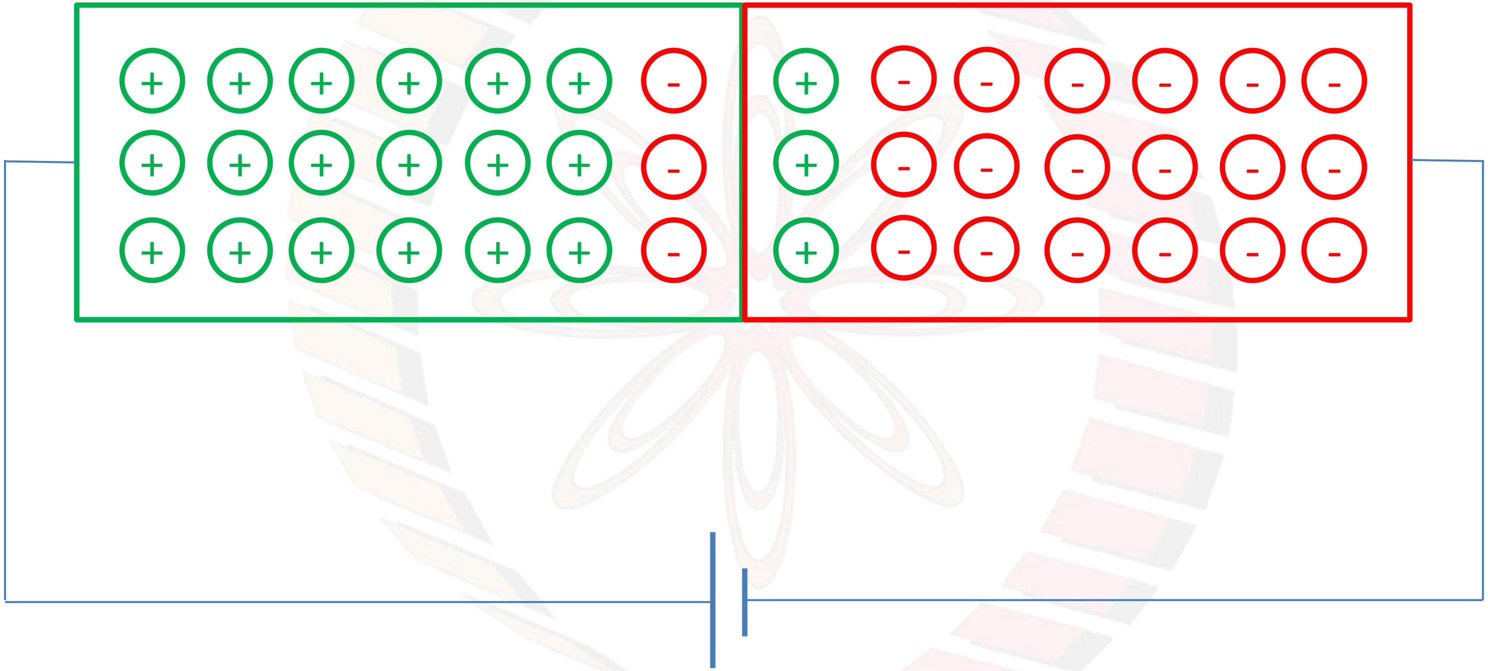
$$\frac{\partial V}{\partial x} = -E$$

$$\frac{\partial_2 V}{\partial x_2} = -\frac{\rho}{\varepsilon}$$

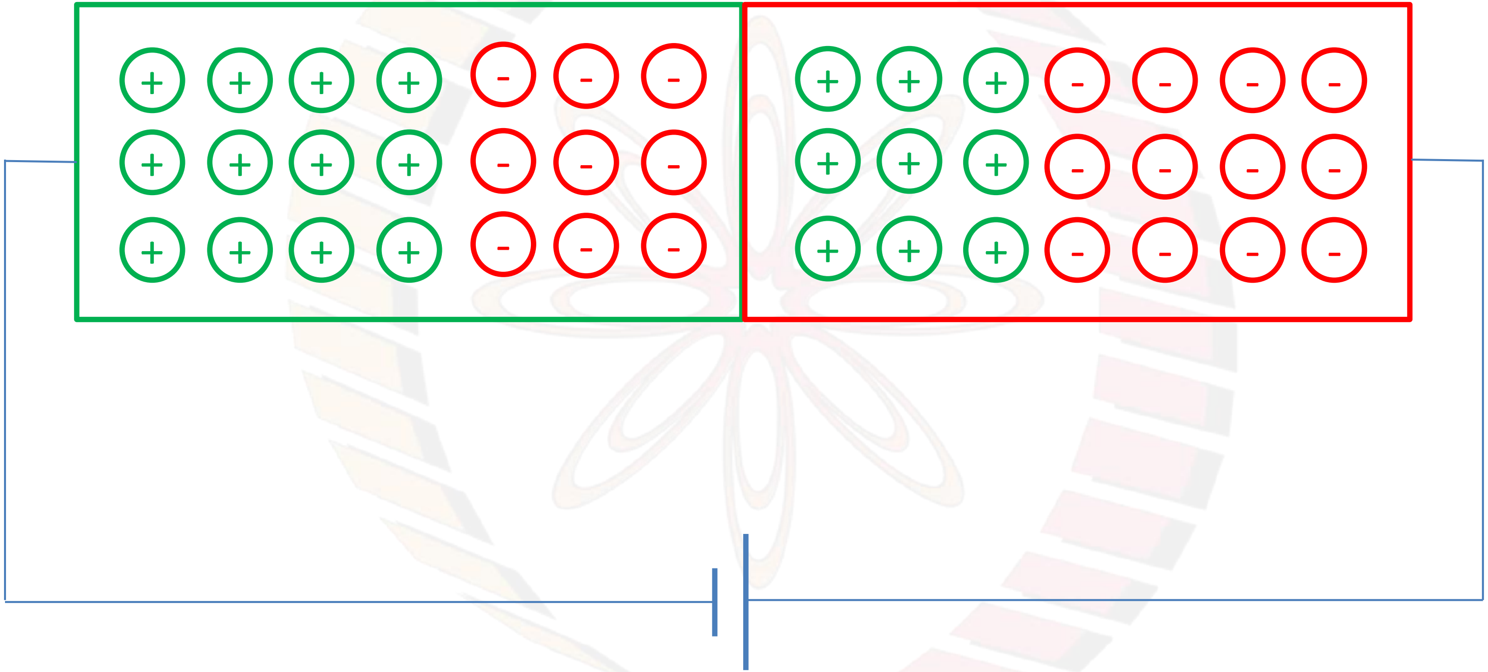
Forward bias



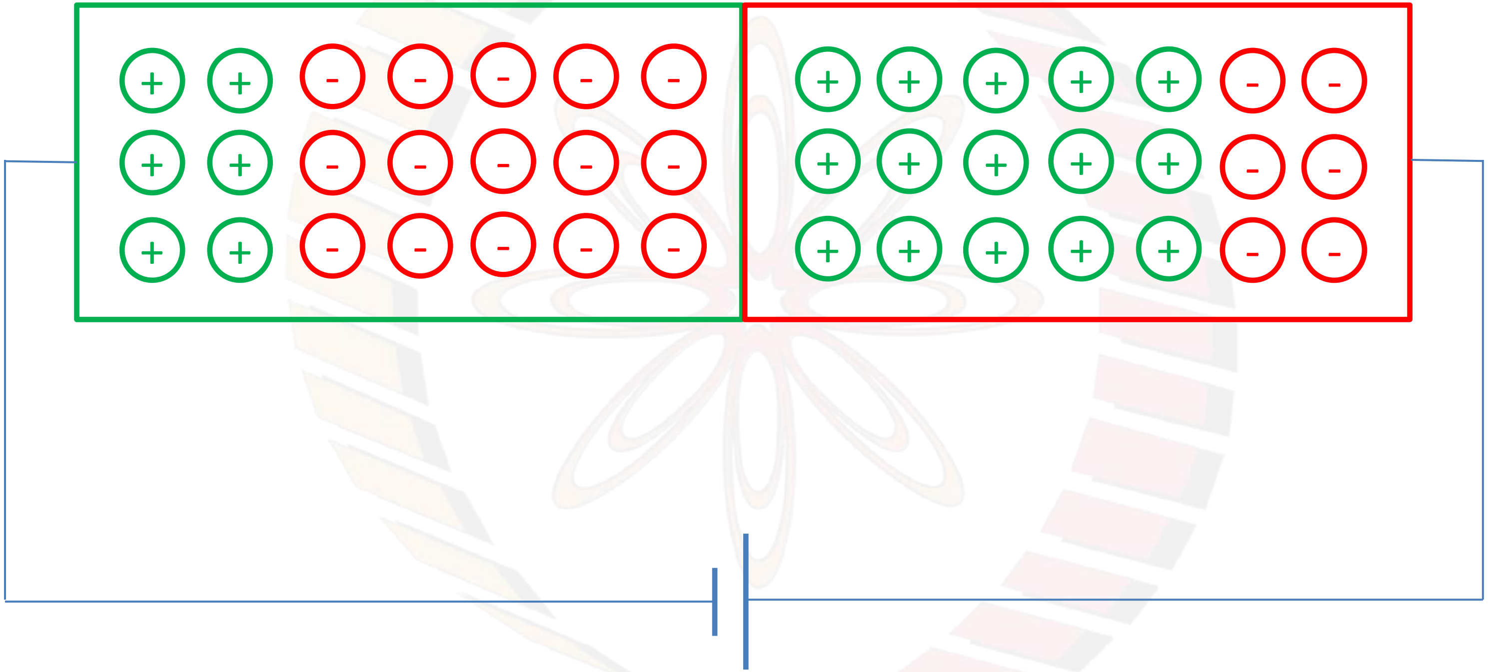
Forward bias



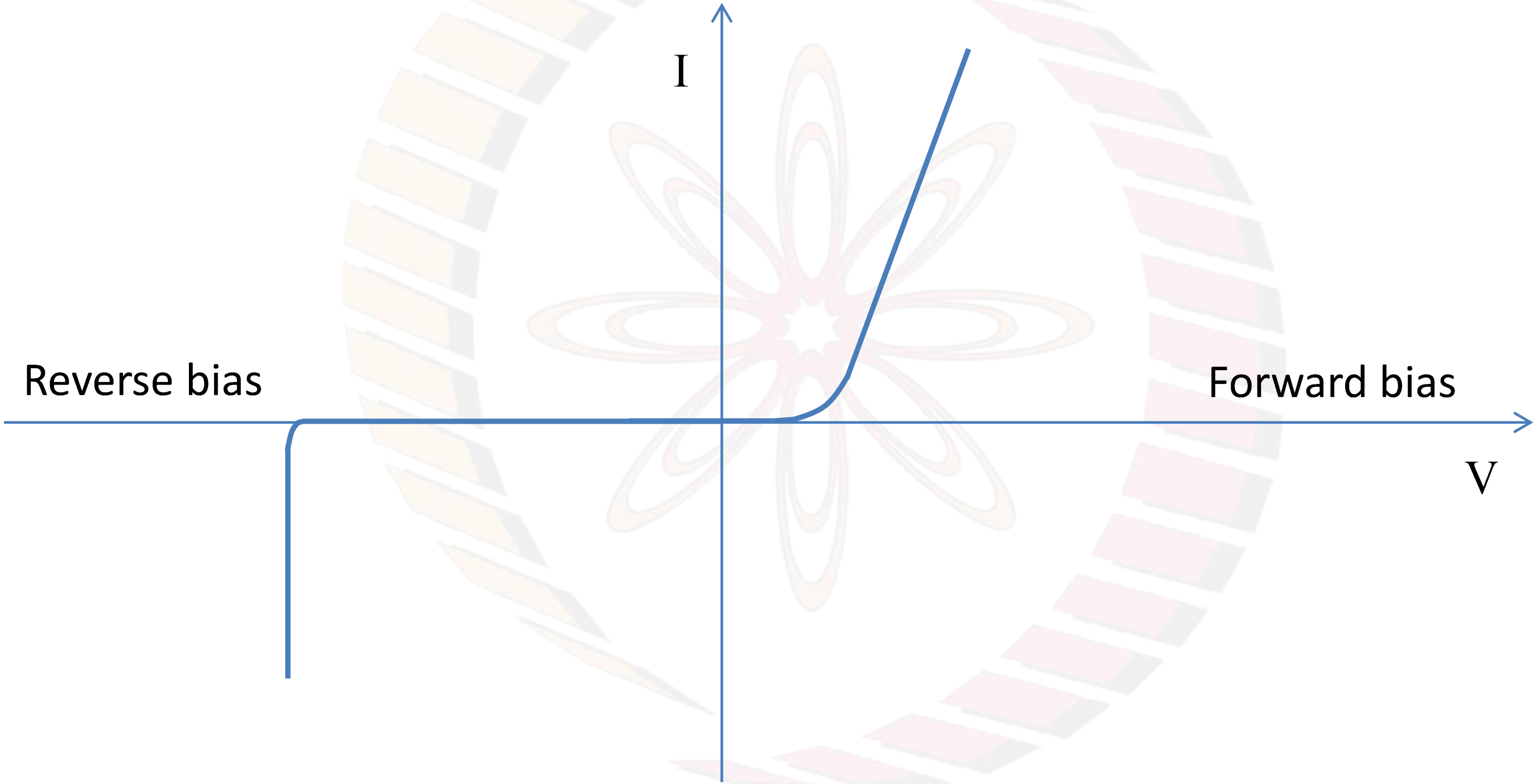
Reverse bias



Reverse bias



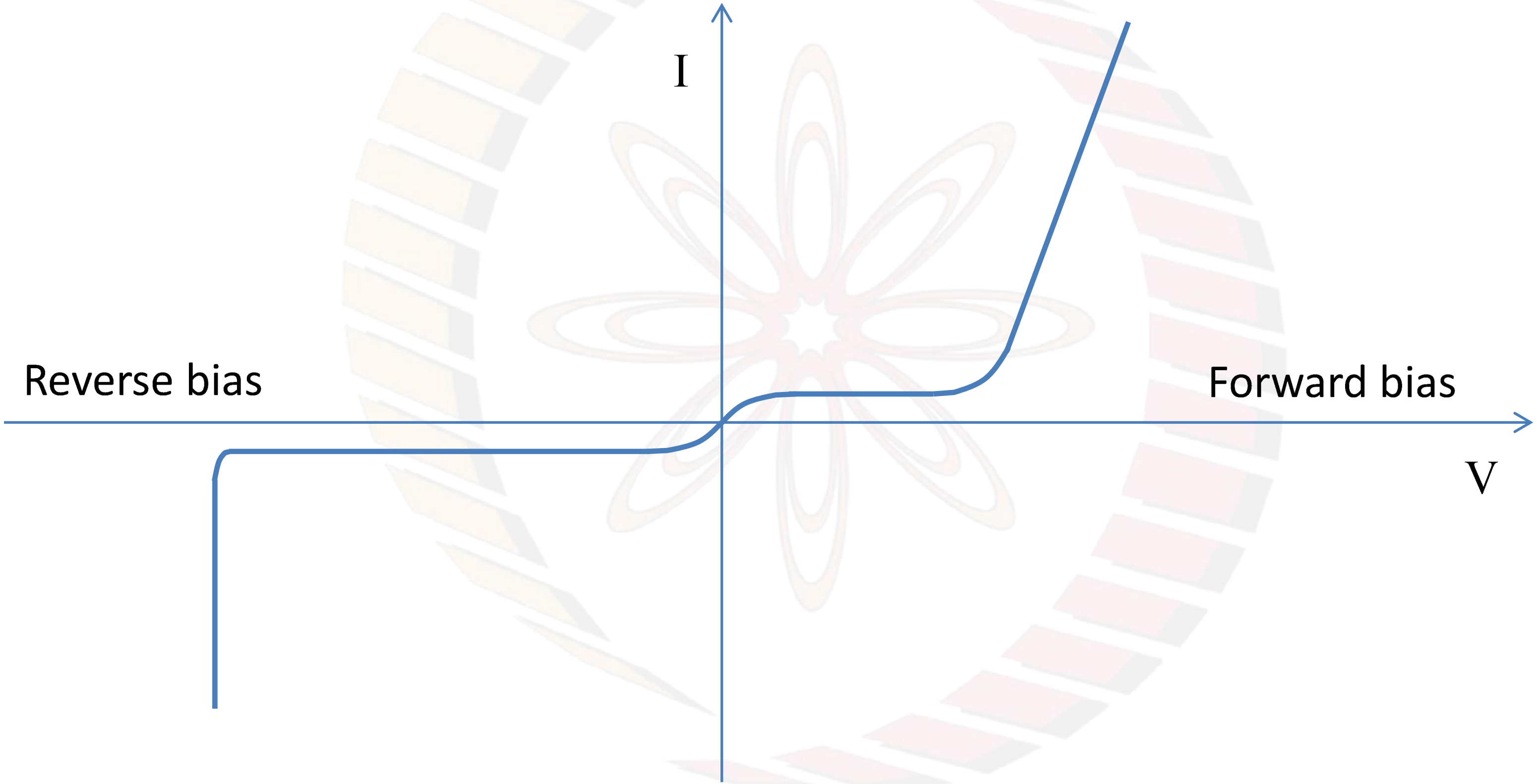
I-V characteristics



Conclusions:

1) A p-n junction can be formed using appropriately doped materials that are processed carefully
2) Charge, Field and Potential depend on the location in a p-n junction
3) A p-n junction has interesting I-V characteristics

I-V characteristics



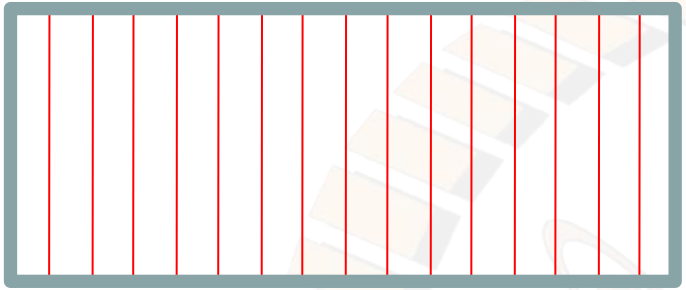
Solar Cell:
Growing the single crystal and making the p-n junction

Learning objectives:

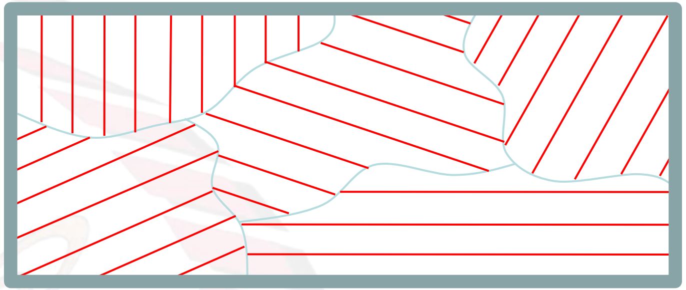
1) To become familiar with the techniques used to make single crystal as well as amorphous Si
2) To understand the method to manufacture the p-n junction

- Czochralski process
- Float Zone process
- Zone refining
- Cutting wafers
- Amorphous Si
- Manufacturing p-n junctions

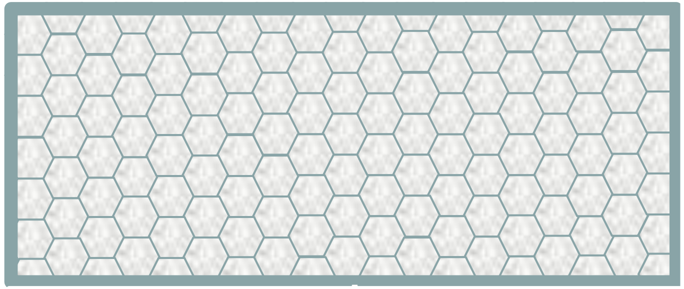
(a)



(b)



(c)



(d)

Quartzite (relatively pure sand) $\rightarrow$ Metallurgical Grade Silicon (MGS)

SiO_2 + Coke + Heat

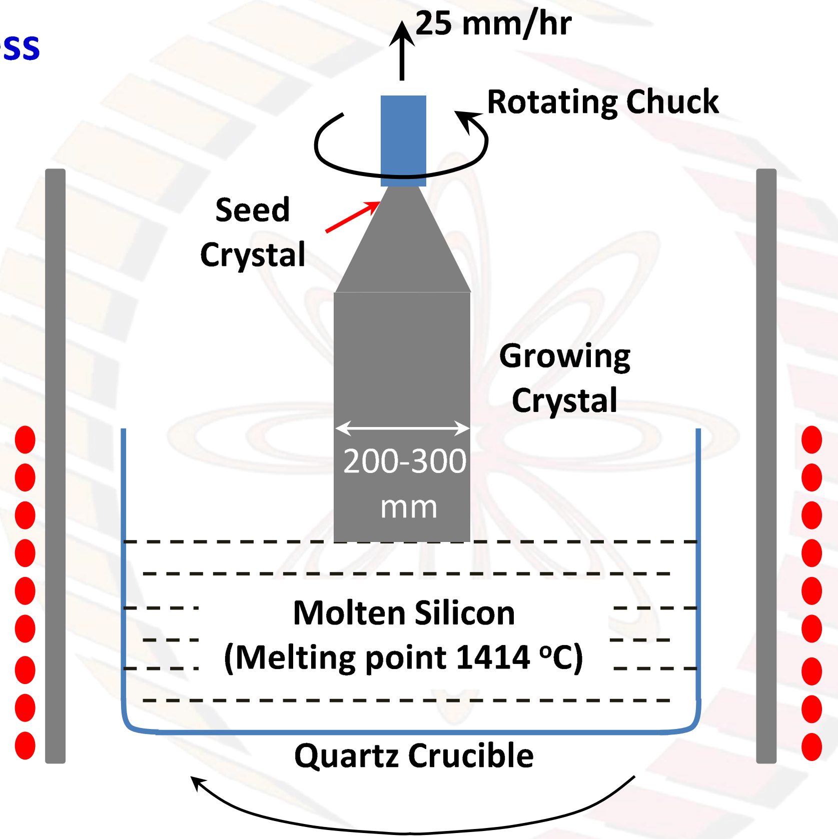
Metallurgical Grade Silicon (MGS) 98% purity $\rightarrow$ Electronic Grade Silicon (EGS) ppm (C, O) to ppb (metals)

$$Si\ (solid) + 3HCl \rightarrow SiHCl_3\ (gas) + H_2$$

Si converted to Trichlorosilane, which is purified and reduced back to Si

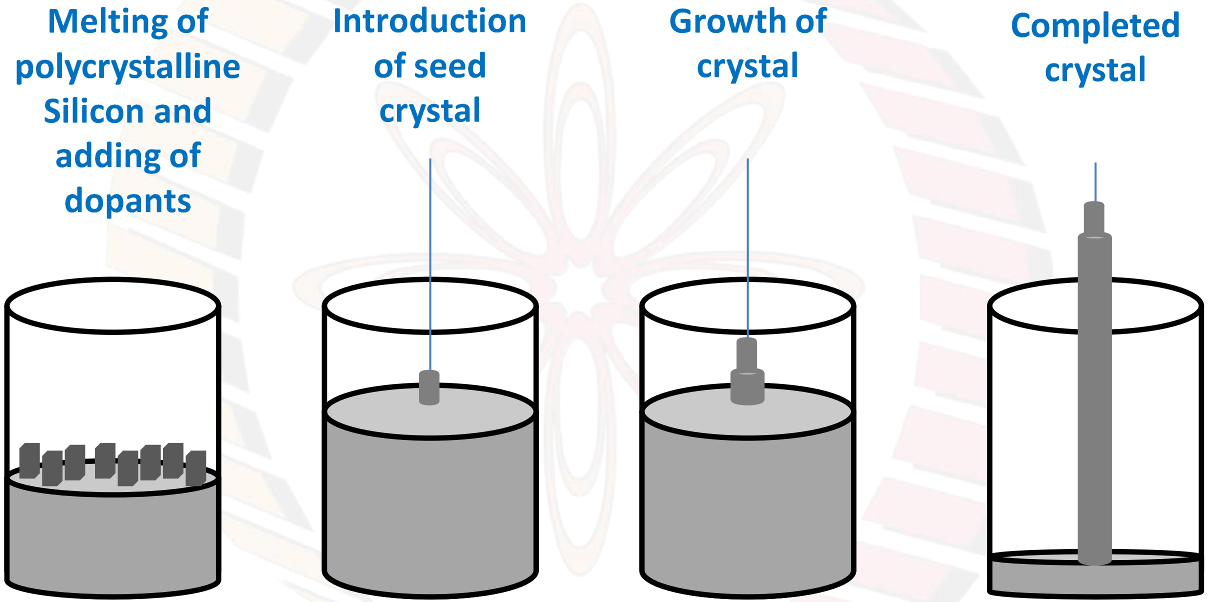
Czochralski process

Semiconductor grade Silicon
Quartz (SiO_2) crucible (1670 °C)
Inert atmosphere of Ar
B or P added before melting



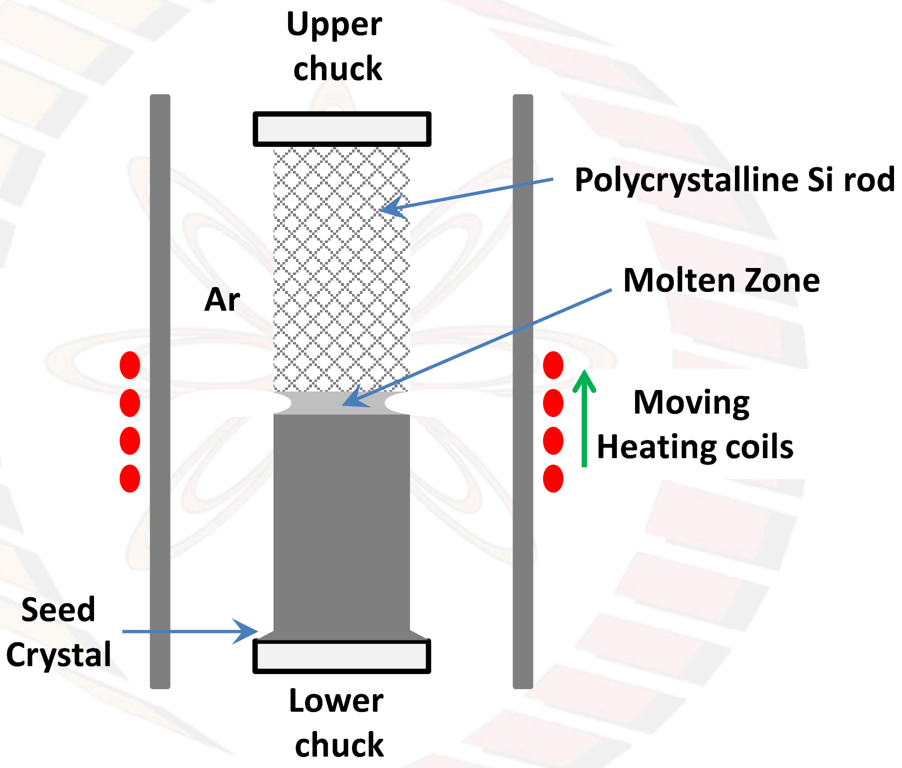
Heating coils
RF currents
Induction
1425 °C

Czochralski process

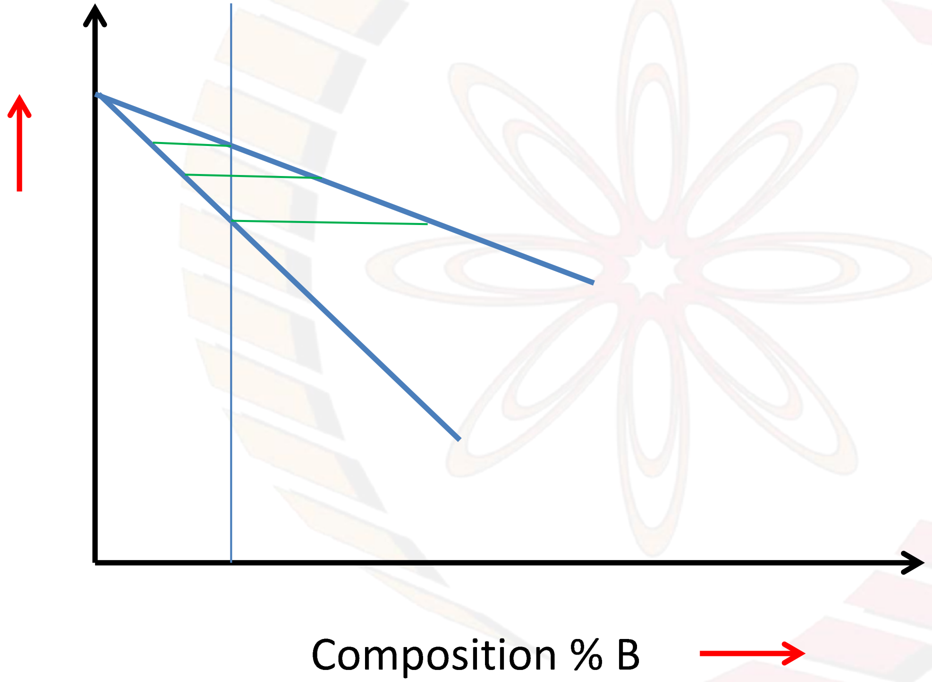


Float zone process

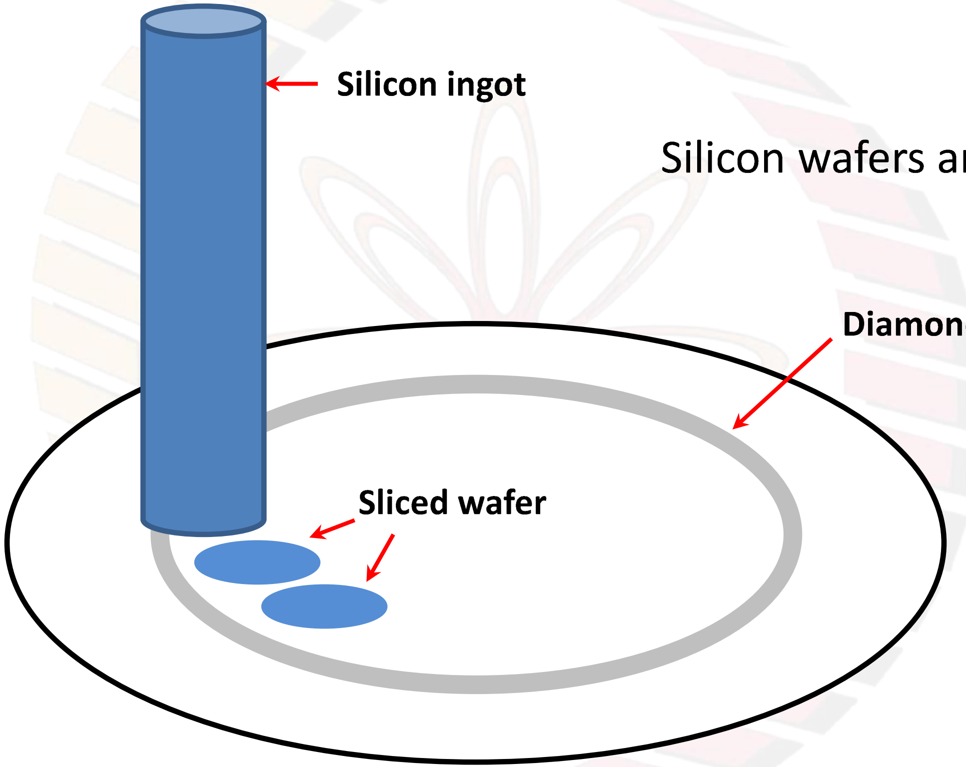
- Smaller diameter (150mm) due to surface tension
- Higher purity



Zone refining



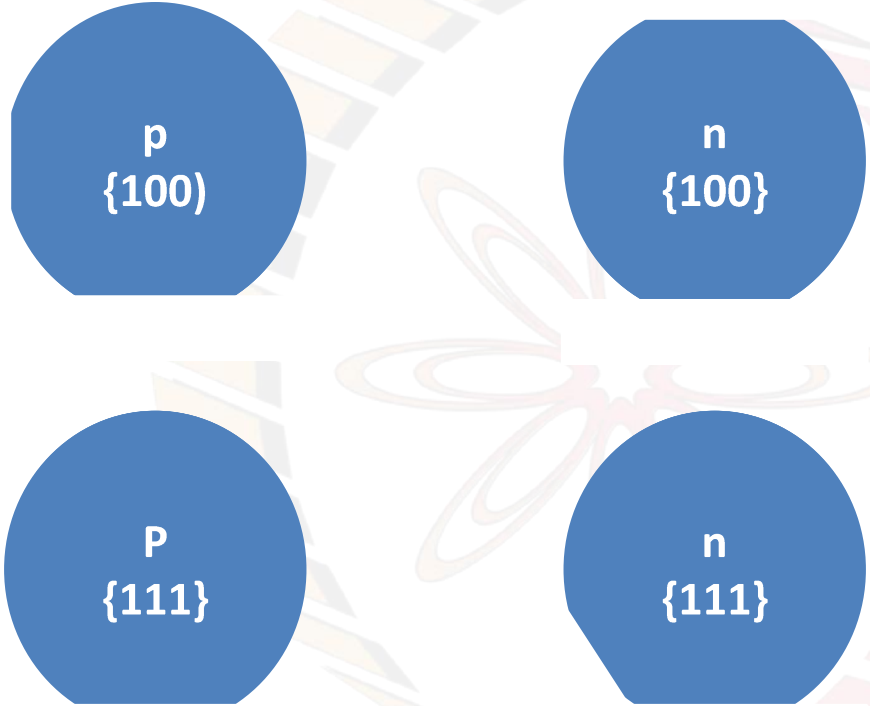
Inner diameter slicing of Si ingot



Silicon wafers are 0.2 to 0.75 mm thick

Can produce one wafer at a time

Wire saw uses fast moving thin wire with abrasive slurry, can cut several wafers at the same time



Notches typically used to indicate orientation and doping

Amorphous Si

CVD process

Has dangling bonds (defects)

Hydrogenated amorphous Silicon, a-Si:H by deposition from Silane gas SiH_4

p-n junction

- Ion implantation: Low temperature process, ionized dopants accelerated using electric fields. Annealing required
- Diffusion: Vapour phase deposition followed by high temperature diffusion
- Epitaxy: Under high vacuum, gaseous elements condense on substrate wafer

Conclusions:

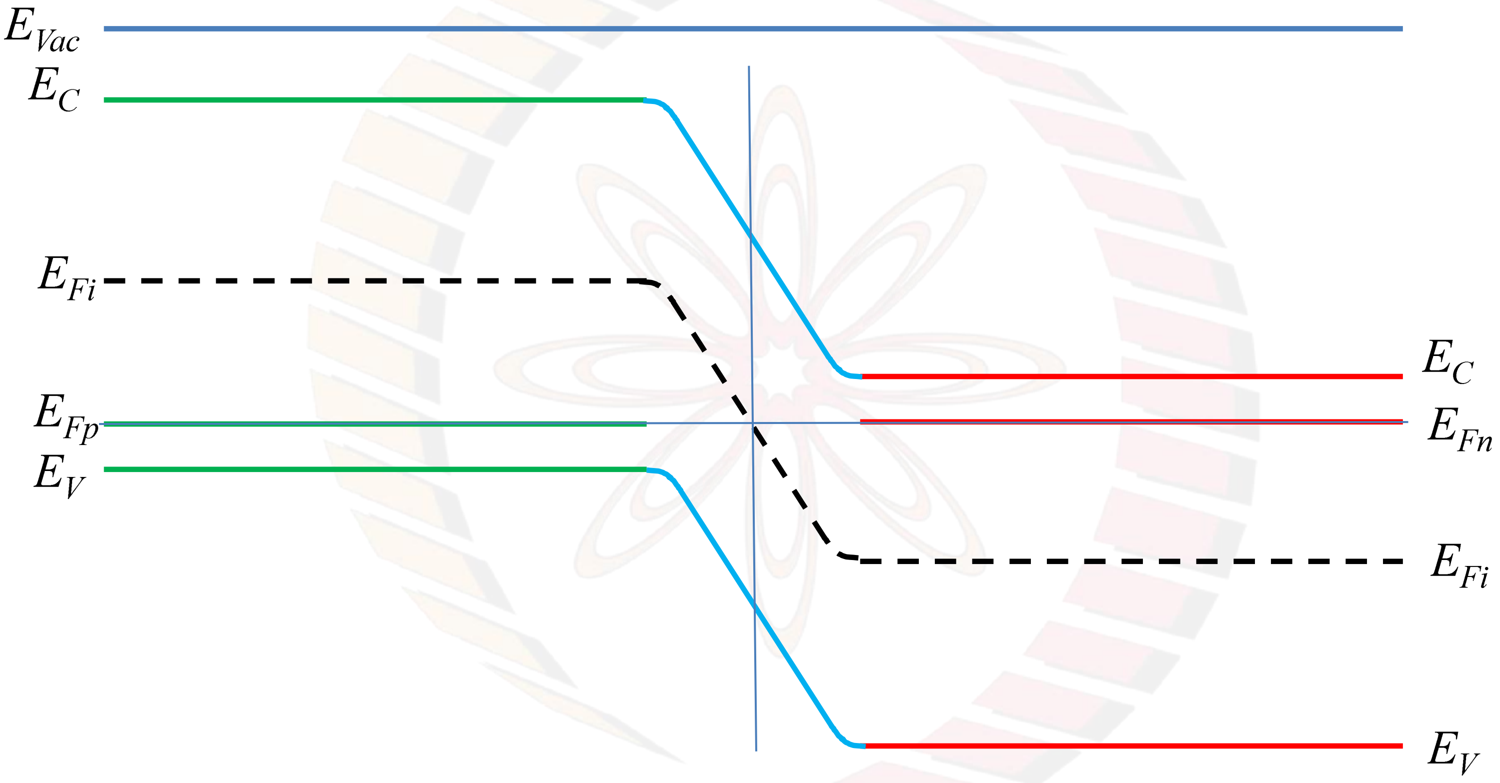
1) It is quite challenging to produce single crystal Si
2) Multiple process steps involved
3) Purity and dimensions can have significant impact on costs
4) Amorphous Si is an option

Solar Energy: Interaction of p-n junction with radiation

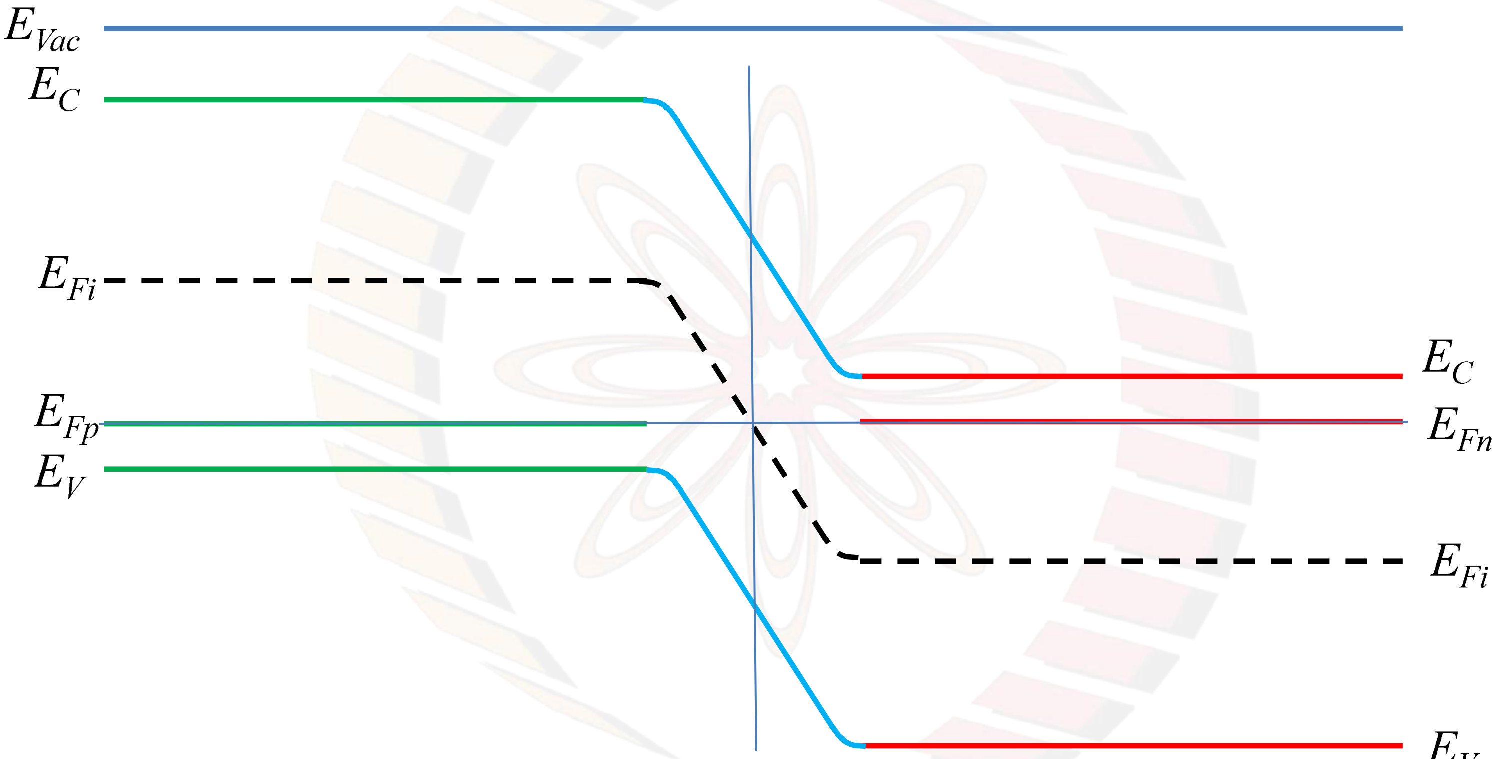
Learning objectives:

1) To describe the interaction of a p-n junction with radiation
2) To explain the functioning of the p-n junction solar cell

Voltage of p-n junction (built in voltage)
Interaction with radiation
OCV
Relation of OCV to bandgap



pn-junction



pn-junction

Conclusions:

1) The p-n junction stabilizes the electron-hole pair
2) To explain the functioning of photovoltaic devices based on their band diagrams

Solar Energy: Interaction of p-n junction solar cell characteristics

Learning objectives:

1) To describe the functioning of a p-n junction based solar cell
2) To explain the characterization of the solar cell

Material systems used
Single crystal Vs Poly Crystal Vs amorphous
Fill factor: Maximum power point
Operation: current source characteristics
Operation: Coupling with end use window of operation
Deterioration

Conclusions:

1) The p-n junction stabilizes the electron-hole pair enabling the solar cell to function
2) The solar cell is a constant current source
3) OCV is not the only parameter to use to characterize the solar cell
4) It is very important to determine fill factor of a solar cell